SPOC - BTS5482SF

SPI Power Controller
For Advanced Front Light Control

Data Sheet

Rev. 1.0, 2013-06-05

Automotive Power

Table of Contents

1 Overview

Features

- 8 bit serial peripheral interface for control and diagnosis
- Integrated control for two external smart power switches
- 3.3 V and 5 V compatible logic pins
- Very low stand-by current
- Enhanced electromagnetic compatibility (EMC) for bulbs as well as LEDs with increased slew rate
- Stable behavior at under voltage
- Device ground independent from load ground
- Green Product (RoHS-Compliant)
- AEC Qualified
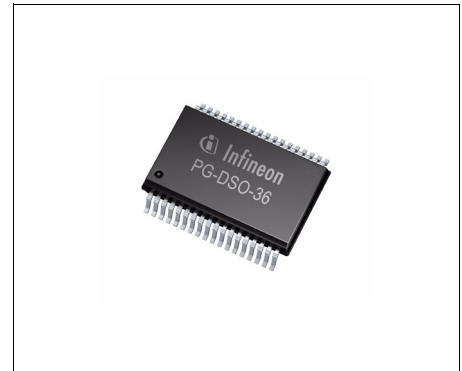
PG-DSO-36-43

Description

The SPOC - BTS5482SF is a four channel high-side smart power switch in PG-DSO-36-43 package providing embedded protective functions. It is especially designed to control standard exterior lighting in automotive applications. In order to use the same hardware, the device can be configured to bulb or LED mode for channel 2 and channel 3. As a result, both load types are optimized in terms of switching and diagnosis behavior.

It is specially designed to drive exterior lamps up to 65W, 27W, 10W and HIDL.

Product Summary

Operating Voltage Power Switch	V_S	4.5 … 28 V
Logic Supply Voltage	V_{DD}	3.0 … 5.5 V
Supply Voltage for Load Dump Protection	$V_{S(LD)}$	40 V
Maximum Stand-By Current at 25 °C	$I_{S(STB)}$	4.5 µA
Typical On-State Resistance at T_j = 25 °C channel 0, 1 channel 2, 3	$R_{DS(ON,typ)}$	4 mΩ 15 mΩ
Maximum On-State Resistance at T_j = 150 °C channel 0, 1 channel 2, 3	$R_{DS(ON,max)}$	8.5 mΩ 28 mΩ
SPI Access Frequency	$f_{SCLK(max)}$	5 MHz

Type	Package	Marking
SPOC - BTS5482SF	PG-DSO-36-43	BTS5482SF

Configuration and status diagnosis are done via SPI. The SPI is daisy chain capable. The device provides a current sense signal per channel that is multiplexed to the diagnosis pin IS. It can be enabled and disabled via SPI commands. An over load and over temperature flag is provided in the SPI diagnosis word. A multiplexed switch bypass monitor provides short-circuit to V_S diagnosis. In OFF-state a current source can be switched to the output of one selected channel in order to detect an open load.

The device provides an external driver capability for two external devices. For each external driver there are two control outputs available: one output for controlling the input and one output for diagnosis enable input. The current sense output of the external smart power drivers can be connected to the IS pin.

The SPOC - BTS5482SF provides a fail-safe feature via limp home input pin.

The power transistors are built by N-channel vertical power MOSFETs with charge pumps.

Protective Functions

- Reverse battery protection with external components
- Reversave™ - Reverse battery protection by self turn-on of channels 0, 1, 2 and 3
- Short circuit protection
- Over load protection
- Thermal shutdown with latch and dynamic temperature protection
- Over current tripping
- Over voltage protection
- Loss of ground protection
- Electrostatic discharge protection (ESD)

Diagnostic Functions

- Multiplexed proportional load current sense signal (IS)
- Enable function for current sense signal configurable via SPI
- High accuracy of current sense signal at wide load current range
- Current sense ratio (k_{ILIS}) configurable for LEDs or bulbs for channel 2 and 3
- Very fast diagnosis in LED mode
- Feedback on over temperature and over load via SPI
- Multiplexed switch bypass monitor provides short circuit to V_S detection
- Integrated, in two steps programmable current source for open load in OFF-state detection

Application Specific Functions

- Fail-safe activation via LHI pin
- Control of two additional loads with external smart power switches

Applications

- High-side power switch for 12 V grounded loads in automotive applications
- Especially designed for standard exterior lighting like high beam, low beam, indicator, parking light and equivalent LED modules.
- Load type configuration via SPI (bulbs or LEDs) for optimized load control
- Replaces electromechanical relays, fuses and discrete circuits

2   Block Diagram
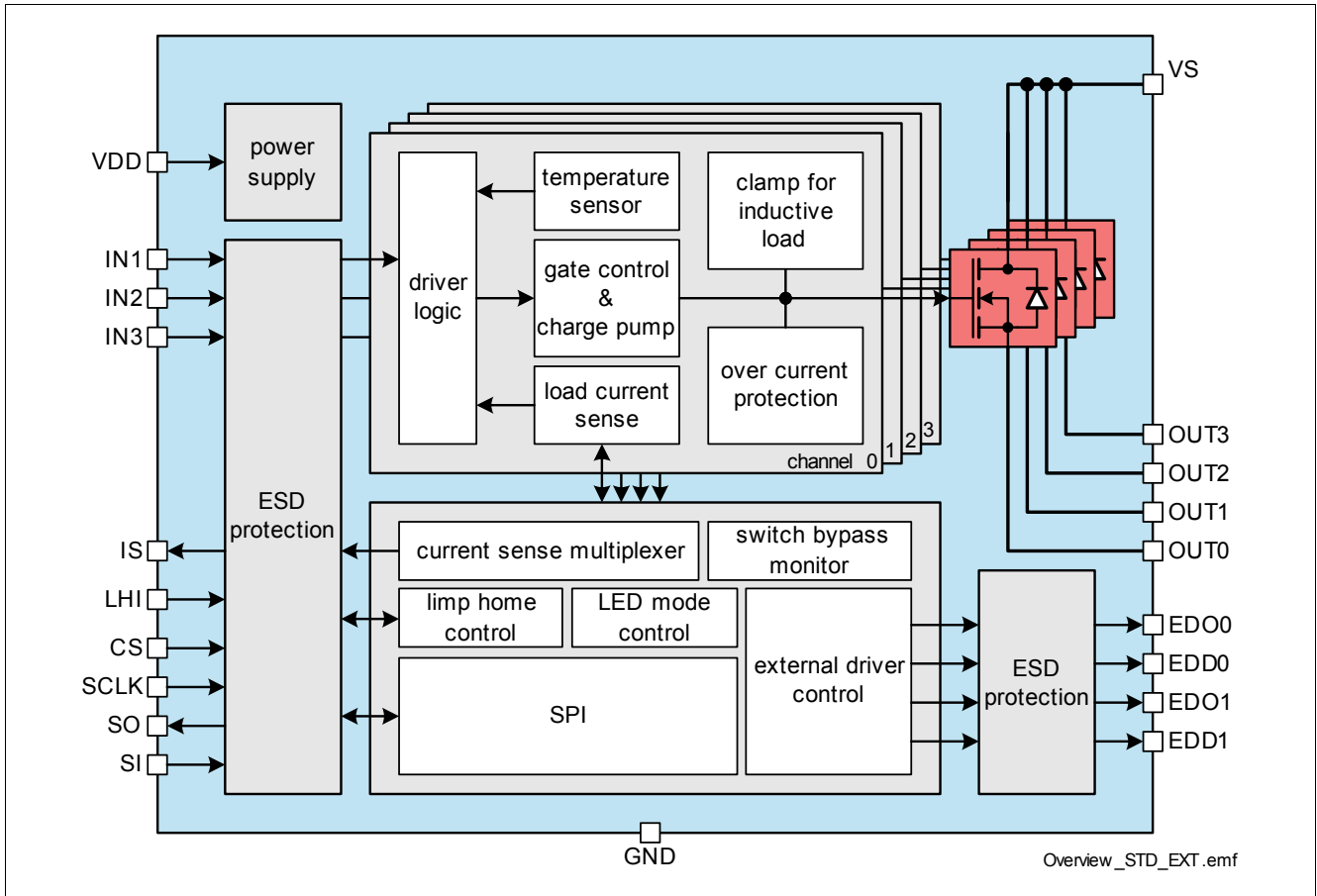
Figure 1   Block Diagram SPOC - BTS5482SF

2.1 Terms

Figure 2 shows all terms used in this data sheet.
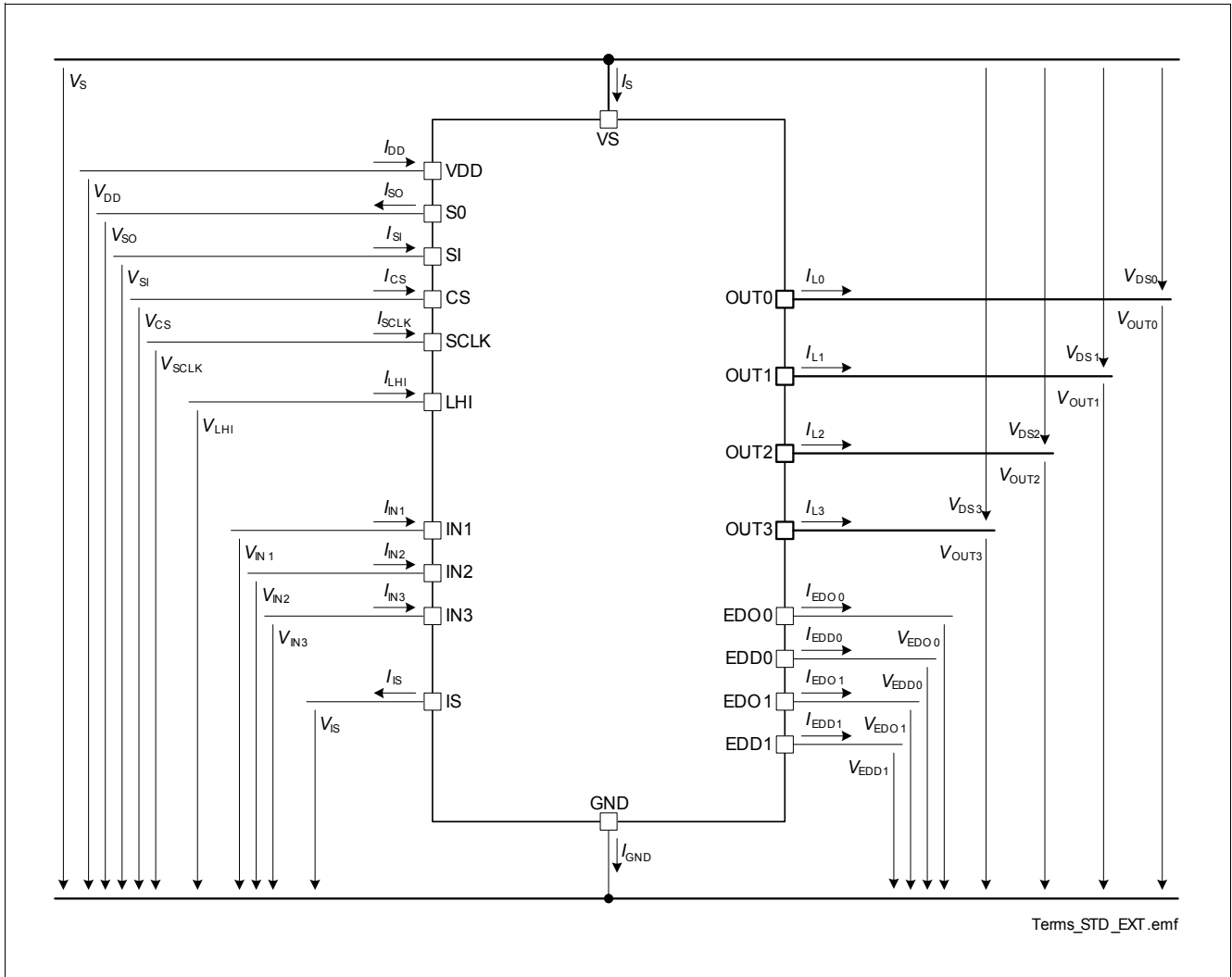
Figure 2   Terms

In all tables of electrical characteristics is valid: Channel related symbols without channel number are valid for each channel separately (e.g. V_{DS} specification is valid for $V_{DS0} \dots V_{DS3}$).

All SPI register bits are marked as follows: `ADDR.PARAMETER` (e.g. `HWCR.CL`). In SPI register description, the values in bold letters (e.g. **0**) are default values.

3 Pin Configuration

3.1 Pin Assignment SPOC - BTS5482SF

(top view)

Left	Pin		Pin	Right
VS	1●		36	VS
VS	2		35	VS
OUT0	3		34	OUT1
OUT0	4		33	OUT1
OUT0	5		32	OUT1
OUT0	6		31	OUT1
OUT3	7		30	OUT2
OUT3	8		29	OUT2
VS	9		28	VS
LHI	10		27	n.c.
SO	11		26	EDO0
SI	12		25	EDD0
SCLK	13		24	EDO1
CS	14		23	EDD1
GND	15		22	GND
IN1	16		21	IS
IN2	17		20	n.c.
IN3	18		19	VDD
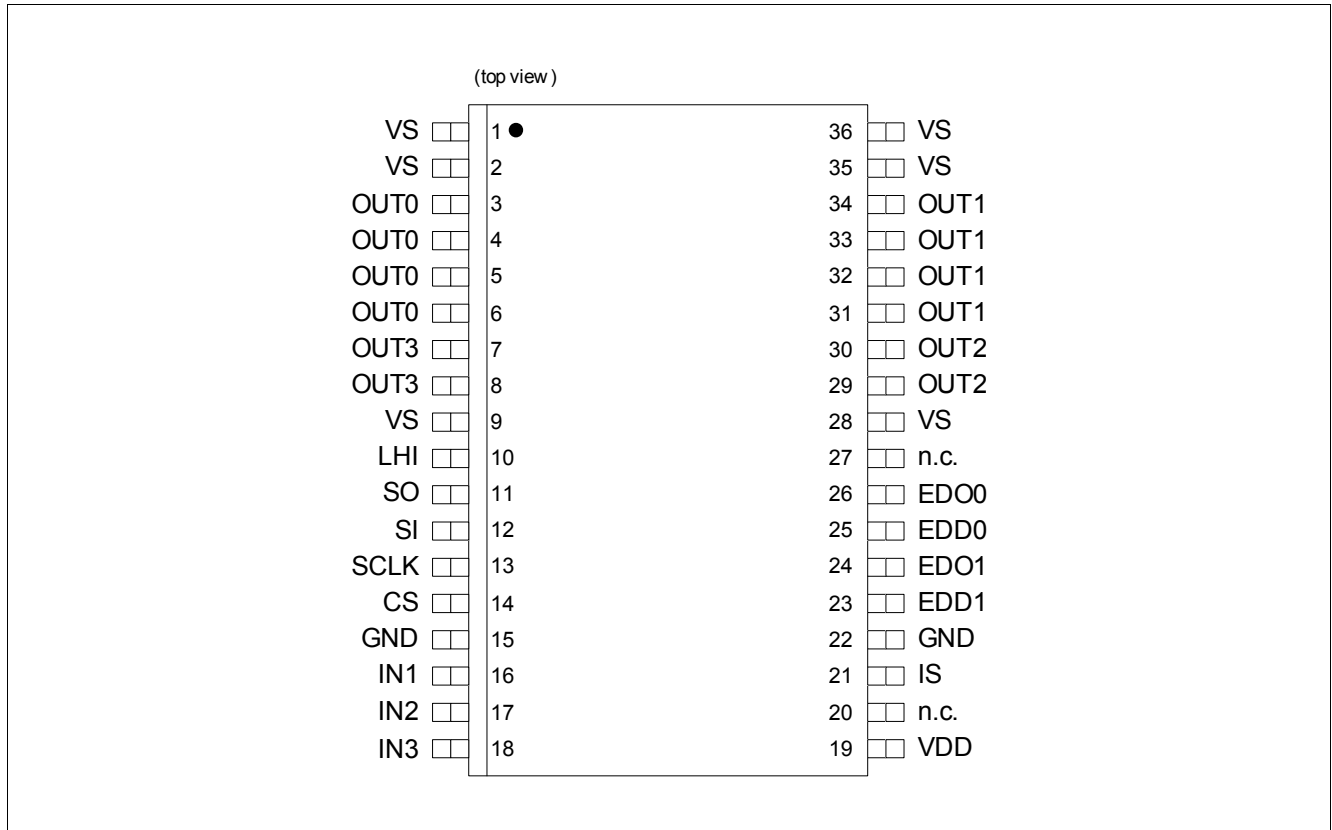
Figure 3 Pin Configuration PG-DSO-36-43

3.2 Pin Definitions and Functions

Pin	Symbol	I/O	Function
Power Supply Pins			
1, 2, 9, 28, 35, 36 [1]	VS	–	Positive power supply for high-side power switch
19	VDD	–	Logic supply (5 V)
15, 22	GND	–	Ground connection
Parallel Input Pins (integrated pull-down, leave unused pins unconnected)			
16	IN1	I	Input signal of channel 1 (high active)
17	IN2	I	Input signal of channel 2 (high active)
18	IN3	I	Input signal of channel 3 (high active)
Power Output Pins			
3, 4, 5, 6 [2]	OUT0	O	Protected high-side power output of channel 0
31, 32, 33, 34 [2]	OUT1	O	Protected high-side power output of channel 1
29, 30 [2]	OUT2	O	Protected high-side power output of channel 2
7, 8 [2]	OUT3	O	Protected high-side power output of channel 3
SPI & Diagnosis Pins			
14	CS	I	Chip select of SPI interface (low active); Integrated pull up
13	SCLK	I	Serial clock of SPI interface
12	SI	I	Serial input of SPI interface (high active)
11	SO	O	Serial output of SPI interface
21	IS	O	Current sense output signal
Limp Home Pin (integrated pull-down, pull-down resistor recommended)			
10	LHI	I	Limp home activation signal (high active)
External Driver Pins (integrated pull-down, leave unused external driver pins unconnected)			
26	EDO0	O	External driver output for activation of external driver 0
24	EDO1	O	External driver output for activation of external driver 1
25	EDD0	O	External driver diagnosis enable signal of external driver 0
23	EDD1	O	External driver diagnosis enable signal of external driver 1
Not connected Pins			
20, 27	n.c.	–	not connected, internally not bonded

1) All VS pins have to be connected.
2) All outputs pins of each channel have to be connected.

4 Electrical Characteristics

4.1 Absolute Maximum Ratings

Absolute Maximum Ratings [1]

T_j = -40 to +150 °C; all voltages with respect to ground

(unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values min.	Limit Values max.	Unit	Conditions
Supply Voltage						
4.1.1	Power supply voltage	V_S	-0.3	28	V	–
4.1.2	Logic supply voltage	V_{DD}	-0.3	5.5	V	–
4.1.3	Reverse polarity voltage according **Figure 31**	$-V_{bat(rev)}$	–	16	V	T_{jStart} = 25 °C $t \le 2$ min. [2]
4.1.4	Supply voltage for short circuit protection (single pulse)	$V_{S(SC)}$			V	R_{ECU} = 20 mΩ l = 0 or 5 m [3]
	channel 0, 1		0	24		R_{Cable} = 6 mΩ/m L_{Cable} = 1 µH/m
	channel 2, 3		0	24		R_{Cable} = 16 mΩ/m L_{Cable} = 1 µH/m
4.1.5	Supply voltage for load dump protection with connected loads	$V_{S(LD)}$	–	40	V	R_I = 2 Ω [4] t = 400 ms
4.1.6	Current through ground pin	I_{GND}	–	25	mA	$t \le 2$ min.
4.1.7	Current through VDD pin	I_{DD}	-25	12	mA	$t \le 2$ min.
Power Stages						
4.1.8	Load current	I_L	–[5]	$I_{L(Htrip)}$	A	[6]
4.1.9	Maximum energy dissipation single pulse	E_{AS}			mJ	[7] $T_{j(0)}$ = 150 °C
	channel 0, 1		–	180		$I_{L(0)}$ = 5 A
	channel 2, 3		–	45		$I_{L(0)}$ = 2 A
4.1.10	Thermal latch restart time	$t_{delay(CL)}$	50	–	ms	
Diagnosis Pin						
4.1.11	Current through sense pin IS	I_{IS}	-8	8	mA	$t \le 2$ min.
Input Pins						
4.1.12	Voltage at input pins	V_{IN}	-0.3	5.5	V	–
4.1.13	Current through input pins	I_{IN}	-0.75 -2.0	0.75 2.0	mA	– $t \le 2$ min.
SPI Pins						
4.1.14	Voltage at chip select pin	V_{CS}	-0.3	V_{DD} + 0.3	V	–
4.1.15	Current through chip select pin	I_{CS}	-2.0	2.0	mA	$t \le 2$ min.
4.1.16	Voltage at serial input pin	V_{SI}	-0.3	V_{DD} + 0.3	V	–
4.1.17	Current through serial input pin	I_{SI}	-2.0	2.0	mA	$t \le 2$ min.
4.1.18	Voltage at serial clock pin	V_{SCLK}	-0.3	V_{DD} + 0.3	V	–
4.1.19	Current through serial clock pin	I_{SCLK}	-2.0	2.0	mA	$t \le 2$ min.

Absolute Maximum Ratings (cont'd)[1]

T_j = -40 to +150 °C; all voltages with respect to ground

(unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values		Unit	Conditions
			min.	max.		
4.1.20	Voltage at serial output pin	V_SO	-0.3	V_DD + 0.3	V	–
4.1.21	Current through serial output pin	I_SO	-2.0	2.0	mA	$t \leq 2$ min.
Limp Home Pin						
4.1.22	Voltage at limp home input pin	V_LHI	-0.3	5.5	V	–
4.1.23	Current through limp home input pin	I_LHI	-0.75	0.75	mA	–
			-2.0	2.0		$t \leq 2$ min.
External Driver Pins						
4.1.24	Voltage at external driver output	V_EDO	-0.3	V_DD + 0.3	V	–
4.1.25	Current through external driver output	I_EDO	-1.0	1.0	mA	$t \leq 2$ min.
4.1.26	Voltage at external driver diagnosis enable	V_EDD	-0.3	V_DD + 0.3	V	–
4.1.27	Current through external driver diagnosis enable	I_EDD	-1.0	1.0	mA	$t \leq 2$ min.
Temperatures						
4.1.28	Junction temperature	T_j	-40	150	°C	–
4.1.29	Dynamic temperature increase while switching	ΔT_j	–	60	K	–
4.1.30	Storage temperature	T_stg	-55	150	°C	–
ESD Susceptibility						
4.1.31	ESD susceptibility HBM	V_ESD			kV	HBM [8]
	OUT pins vs. VS		-4	4		–
	other pins incl. OUT vs. GND		-2	2		–

1) Not subject to production test, specified by design.
2) Device is mounted on an FR4 2s2p board according to Jedec JESD51-2,-5,-7 at natural convection; The product (chip+package) was simulated on a 76.4 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70 µm Cu, 2 x 35 µm Cu). Where applicable, a thermal via array under the package contacted the first inner copper layer.
3) In accordance to AEC Q100-012 and AEC Q101-006.
4) R_I is the internal resistance of the load dump pulse generator.
5) No protection mechanism available. Inverse current needs to be limited by external circuitry to prevent overheating.
6) Over current protection is an integrated protection function.
7) Pulse shape represents inductive switch off: $I_\text{D(t)} = I_\text{D}(0) \times (1 - t / t_\text{pulse})$; $0 < t < t_\text{pulse}$
8) ESD resistivity, HBM according to ANSI/ESDA/JEDEC JS-001-2010

Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

4.2 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to **www.jedec.org**.

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Typ.	Max.		
4.2.1	Junction to Soldering Point [1]	R_{thJSP}	–	–	20	K/W	measured to pin 1, 2, 9, 28, 35, 36
4.2.2	Junction to Ambient [1]	R_{thJA}	–	35	–	K/W	[2]

1) Not subject to production test, specified by design.

2) Specified R_{thJA} values is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; The product (chip+package) was simulated on a 76.4 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70 µm Cu, 2 x 35 µm Cu). Where applicable, a thermal via array under the package contacted the first inner copper layer.

5 Power Supply

The SPOC - BTS5482SF is supplied by two supply voltages V_S and V_{DD}. The V_S supply line is used by the power switches. The V_{DD} supply line is used by the SPI related circuitry and for driving the SO line. A capacitor between pins VDD and GND is recommended as shown in **Figure 31**.

There is a power-on reset function implemented for the V_{DD} logic power supply. After start-up of the logic power supply, all SPI registers are reset to their default values. The SPI interface including daisy chain function is active as soon as V_{DD} is provided in the specified range independent of V_S. First SPI data are the output register values for internal channels with TER = 1.

Specified parameters are valid for the supply voltage range according $V_{S(nor)}$ or otherwise specified. For the extended supply voltage range according $V_{S(ext)}$ device functionality (switching, diagnosis and protection functions) are still given, parameter deviations are possible.

5.1 Power Supply Modes

The following table shows all possible power supply modes for V_S, V_{DD} and the pin LHI.

Power Supply Modes	Off	Off	SPI on	Reset	Off	On via INx	Limp Home mode without SPI	Normal operation	Limp Home mode with SPI [1]
V_S	0 V	0 V	0 V	0 V	13.5 V	13.5 V	13.5 V	13.5 V	13.5 V
V_{DD}	0 V	0 V	5 V	5 V	0 V	0 V	0 V	5 V	5 V
LHI	0 V	5 V	0 V	5 V	0 V	0 V	5 V	0 V	5 V
Power stage, protection	–	–	–	–	–	✓ [2]	✓ [2]	✓	✓ [2]
Limp home	–	–	–	–	–	–	✓	–	✓
SPI (logic)	–	–	✓	✓	reset	reset	reset	✓	reset [3]
Stand-by current	–	–	–	–	✓	✓ [4]	–	✓ [5]	–
Idle current	–	–	–	–	–	–	–	✓ [6]	–
Diagnosis	–	–	–	–	–	–	–	✓	✓ [7]

1) SPI read only
2) Channel 1, 2 and/or 3 activated according to the state of INx
3) SPI reset only with applied V_S voltage
4) When INx = 0 V
5) When DCR.MUX = 111_b and INx = 0 V
6) When all channels are in OFF-state and DCR.MUX $\neq 111_b$
7) Current sense disabled in limp home mode

5.1.1 Stand-by Mode and Device Wake-up Mechanisms

Stand-by mode is entered as soon as the current sense multiplexer (DCR.MUX) is in default (stand-by) position and all input pins are not set. All error latches are cleared automatically in stand-by mode. As soon as stand-by mode is entered, register HWCR.STB is set. To wake-up the device, the current sense multiplexer (DCR.MUX) is programmed different to default (stand-by) position. The power-on wake up time $t_{WU(PO)}$ has to be considered.

Idle mode parameters are valid, when all channels are switched off, whereas the current sense multiplexer is not in default position, and V_{DD} supply is available.

Note: A transition from operation to stand-by mode does not reset the SPI registers. So, if V_{DD} is present and SPI is programmed, a changing to MUX = 111_b does not reset the SPI registers. An activation of the channels via the input pin INx will wake up the device with the former SPI register settings.

Activating one of the outputs via the input pins (INx = high) will wake-up the device out of stand-by mode. The power stages are working without VDD supply according to the table in **Chapter 5.1**. The output turn-on time will be extended by the stand-by channel wake up time $t_{WU(STCH)}$ as long as no other channel is active. If one channel is active already before, channel turn-on times t_{ON} (**6.6.12**) can be considered.

Note: In the operation with V_{DD} = 0 V and INx = high a switching off of all input signals will turn the device in stand-by mode. In stand-by mode the error latches are cleared.

Limp home (LHI = high) applied for a time longer than $t_{LH(ac)}$ will wake-up the device out of stand-by mode after the power-on wake up time $t_{WU(PO)}$ and it is working without VDD supply. Channels 1, 2 and 3 can be activated via the input pins INx. The error latches can be cleared by a low-high transition at the according input pin.

5.2 Reset

There are several reset triggers implemented in the device. They reset the SPI registers including the over temperature latches to their default values. The power stages will switch off, if they are activated via the SPI register `OUTL.n`. If the power stages are activated via the parallel input pins they are not affected by the reset signals. The ERR-flags are cleared by those reset triggers. The over temperature protection and latches are functional after a reset trigger.

Note: During a reset only the channels 1, 2 and 3 can be activated via the according input pins. The input assigned mode is not available during a reset.

The first SPI transmission after any kind of reset contains at pin SO the read information from the standard diagnosis, the transmission error bit `TER` is set.

Power-On Reset

The power-on reset is released, when V_{DD} voltage level is higher than $V_{DD(PO)}$. The SPI interface can be accessed after wake up time $t_{WU(PO)}$. If one of the parallel input pins INx or the LHI pin is high, the power-on reset is not affecting the protection latches.

Reset Command

There is a reset command available to reset all register bits of the register bank and the diagnosis registers. As soon as `HWCR.RST = 1`$_b$, a reset, equivalent to power-on reset is executed. The SPI interface can be accessed after transfer delay time $t_{CS(td)}$.

Limp Home Mode

The limp home mode will be activated as soon as the pin LHI is set to high for a time longer than $t_{LH(ac)}$. The SPI write-registers are reset with applied V_S voltage and the protection latches are cleared. The outputs OUT1 to OUT3 can be activated via the input pins also during activated limp home mode. The error latches can be cleared by a low-high transition at the according input pin. For application example see **Figure 31**. The SPI interface is operating normally, so the limp home register bit LHI as well as the error flags can be read, but any write command will be ignored.

5.3 Electrical Characteristics

Electrical Characteristics Power Supply

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
5.3.1	Supply voltage range for normal operation power switch	$V_{S(nor)}$	8	–	17	V	–
5.3.2	Extended supply voltage range for operation power switch	$V_{S(ext)}$	4.5[1]	–	28[2]	V	Parameter deviations possible
5.3.3	Undervoltage shutdown	$V_{S(UV)}$	–	3.7	–	V	
5.3.4	Stand-by current for whole device with loads	$I_{S(STB)}$				µA	V_{DD} = 0 V V_{LHI} = 0 V
			–	–	4.5		[2] T_j = 25 °C
			–	–	28		[2] T_j ≤ 85 °C
5.3.5	Idle current for whole device with loads, all channels off	$I_{S(idle)}$	–	14.5	–	mA	V_{DD} = 5 V `DCR.MUX = 110`
5.3.6	Logic supply voltage	V_{DD}	3.0	–	5.5	V	–
5.3.7	Logic supply current	I_{DD}				µA	[3]V_{LHI} = 0 V V_{DD} = 5 V V_{IS} = 0 V Chip in Idle f_{SCLK} = 0 Hz V_{CS} = 5 V f_{SCLK} = 5 MHz V_{CS} = 0 V
			–	80	200		
			–	350	500		
5.3.8	Logic stand-by current	$I_{DD(STB)}$	–	25	–	µA	V_{CS} = V_{DD} f_{SCLK} = 0 Hz Chip in Stand-by
5.3.9	Operating current for whole device active	I_{GND}	–	15	21	mA	f_{SCLK} = 0 Hz
LHI Input Characteristics							
5.3.10	L-input level at LHI pin	$V_{LHI(L)}$	0	–	0.8	V	–
5.3.11	H-input level at LHI pin	$V_{LHI(H)}$	1.8	–	5.5	V	–
5.3.12	L-input current through LHI pin	$I_{LHI(L)}$	3	8	20	µA	[2] V_{LHI} = 0.6 V
5.3.13	H-input current through LHI pin	$I_{LHI(H)}$	10	40	80	µA	V_{LHI} = 5 V
Reset							
5.3.14	Power-On reset threshold voltage	$V_{DD(PO)}$	–	–	2.4	V	–
5.3.15	Power-On wake up time	$t_{WU(PO)}$	–	–	200	µs	[2]
5.3.16	Stand-by channel wake up time	$t_{WU(STCH)}$	–	–	200	µs	[2]
5.3.17	Limp home acknowledgement time	$t_{LH(ac)}$	5	–	200	µs	[2]

1) Load current sense diagnosis is not available for V_S < 6.0 V

2) Not subject to production test, specified by design.

3) Device in normal operation without any temperature or overcurrent latches set

Note: Characteristics show the deviation of parameter at the given supply voltage and junction temperature.

6 Power Stages

The high-side power stages are built by N-channel vertical power MOSFETs (DMOS) with charge pumps. There are four channels implemented in the device.

6.1 Output ON-State Resistance

The on-state resistance $R_{DS(ON)}$ depends on the supply voltage V_S as well as on the junction temperature T_j. **Figure 4** shows those dependencies. The behavior in reverse polarity mode is described in **Section 7.6**.
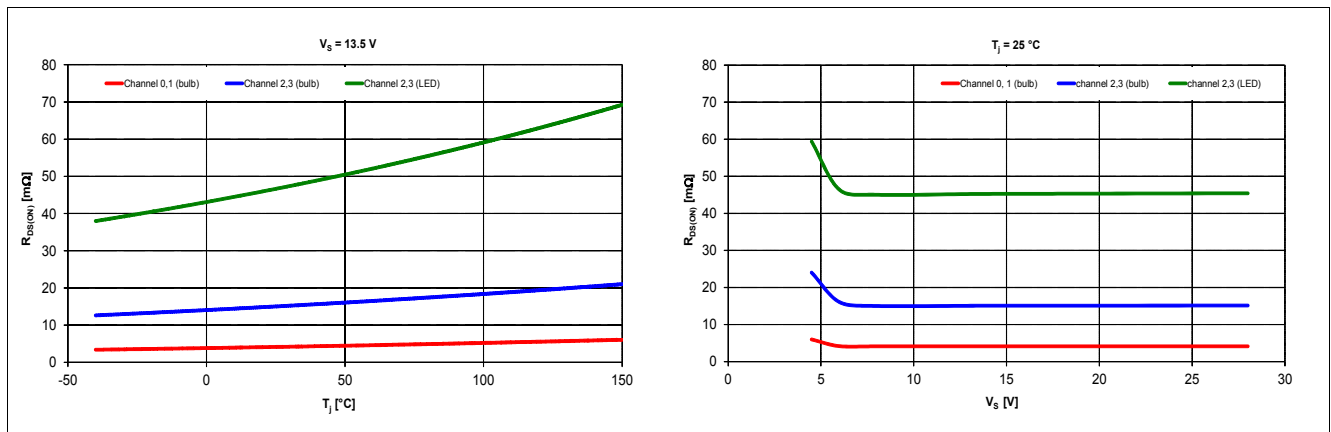

Figure 4   Typical On-State Resistance

6.2 Input Circuit

The outputs of the SPOC - BTS5482SF can be activated either via the SPI register OUTL.OUTn or via the dedicated input pins. There are two different ways to use the input pins, the direct drive mode and the assigned drive mode. The default setting is the direct drive mode. To activate the assigned drive mode the register bit ICR.INCG needs to be set.

Additionally, there are two ways of using the input pins in combination with the OUTL register by programming the ICR.COL parameter.

- ICR.COL = 0_b: A channel is switched on either by the according OUTL register bit or the input pin.
- ICR.COL = 1_b: A channel is switched on by the according OUTL register bit only, when the respective input pin is high. In this configuration, a PWM signal can be applied to the input pin and the channel is activated by the SPI register OUTL.
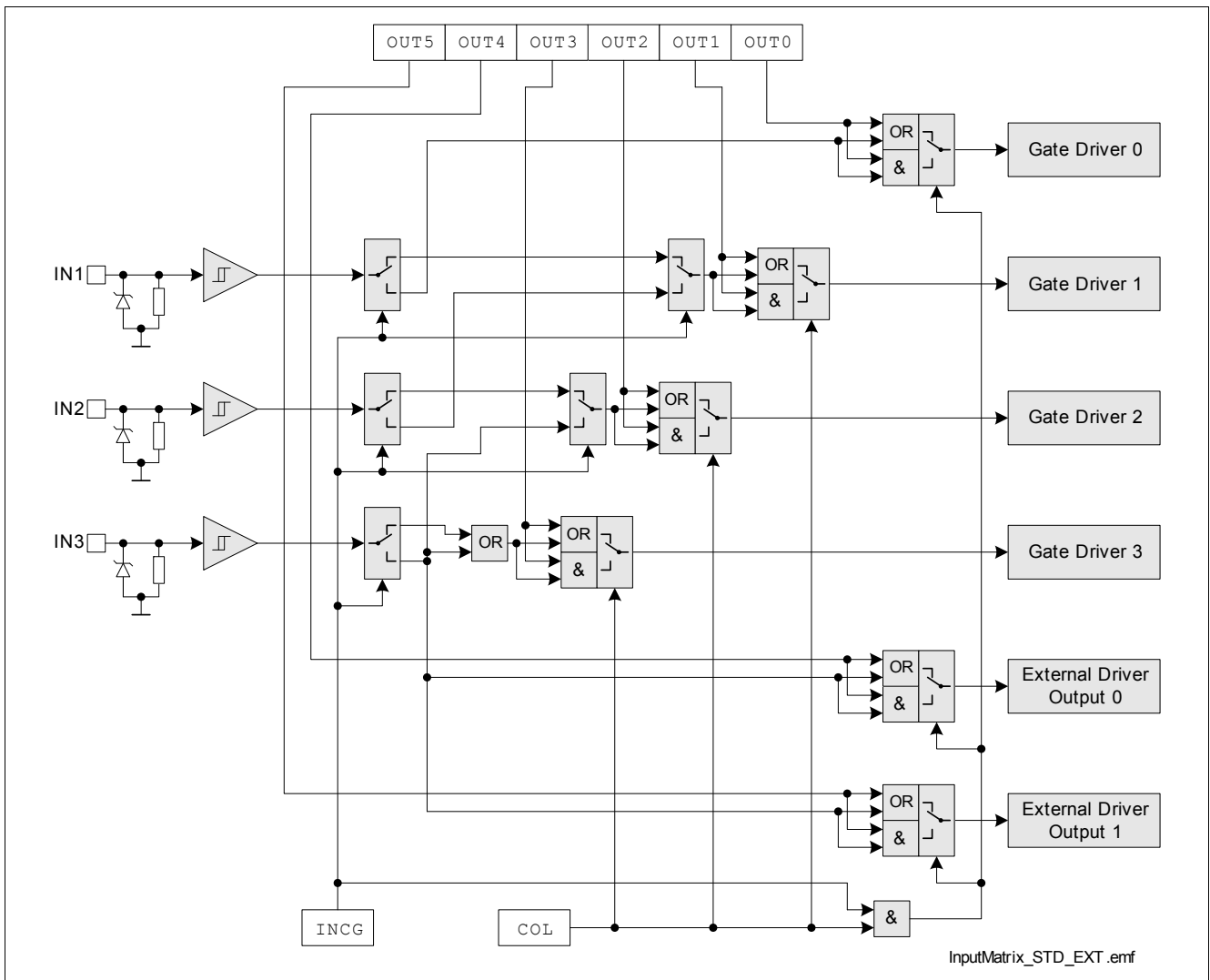
Figure 5 shows the complete input switch matrix.

Figure 5   Input Switch Matrix

The current sink to ground ensures that the input signal is low in case of an open input pin. The zener diode protects the input circuit against ESD pulses.

6.2.1   Input Direct Drive

This mode is the default after the device's wake up and reset. The input pins activate the channels during normal operation (with default setting of bit `ICR.INCG`), stand-by mode and limp home mode. Channel 0 and the external drivers can be activated only via the SPI-bit `OUTx.OUTn` in direct drive mode. The inputs are linked directly to the channels according to:

Table 1   Direct Drive Mode

Input Pin	Assigned channel, if $ICR.INCG = 0_b$
IN1	Channel 1
IN2	Channel 2
IN3	Channel 3

6.2.2 Input Assigned Drive

To activate the assigned drive function the register bit `ICR.INCG` needs to be set. In this mode all output channels can be activated via the input pins. Channel 2, 3 and the two external drivers are assigned to only one input pin. The following mapping is used:

Table 2   Assigned Drive Mode

Input Pin	Assigned channel, if `ICR.INCG = 1`$_b$
IN1	Channel 0
IN2	Channel 1
IN3	Channel 2, channel 3, external driver 0, external driver 1

6.3 Power Stage Output

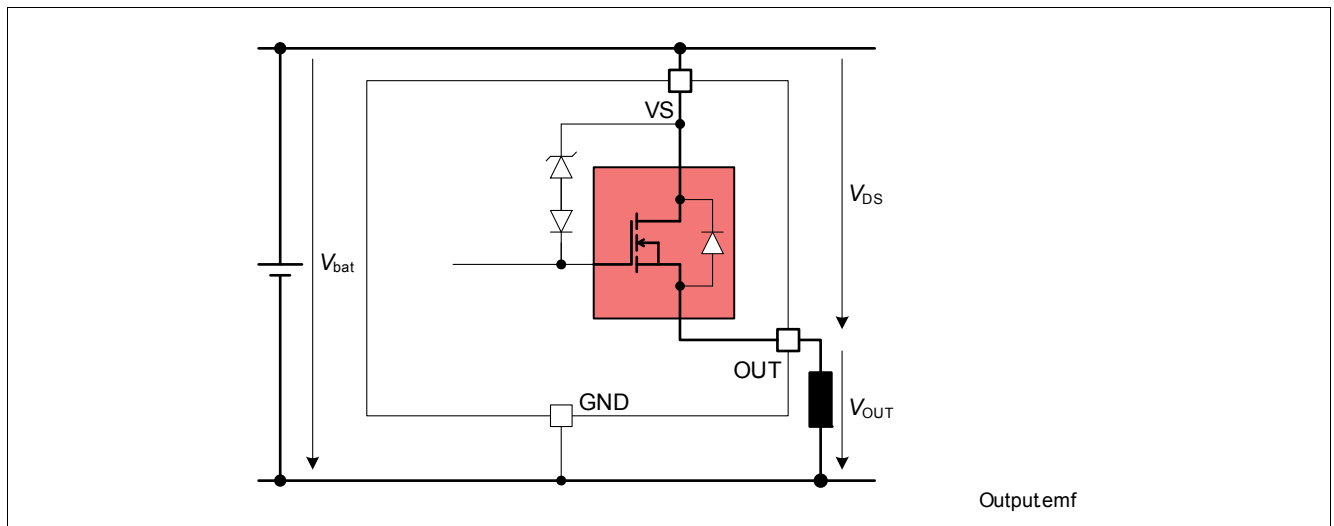The power stages are built to be used in high side configuration (**Figure 6**).

Figure 6   Power Stage Output

The power DMOS switches with a dedicated slope, which is optimized in terms of electromagnetic emission (EME). Defined slew rates and edge shaping allow lowest EME during PWM operation at low switching losses.

6.3.1 Bulb and LED mode

Channel 2 and channel 3 can be configured in bulb and LED mode via the SPI registers `HWCR.LEDn`. During LED mode following parameters are changed for an optimized functionality with LED loads: On-state resistance $R_{DS(ON)}$, switching timings ($t_{delay(ON)}$, $t_{delay(OFF)}$, t_{ON}, t_{OFF}), slew rates dV/dt_{ON} and dV/dt_{OFF}, current protections $I_{L(trip)}$ and current sense ratio k_{ILIS}.

6.3.2 Switching Resistive Loads

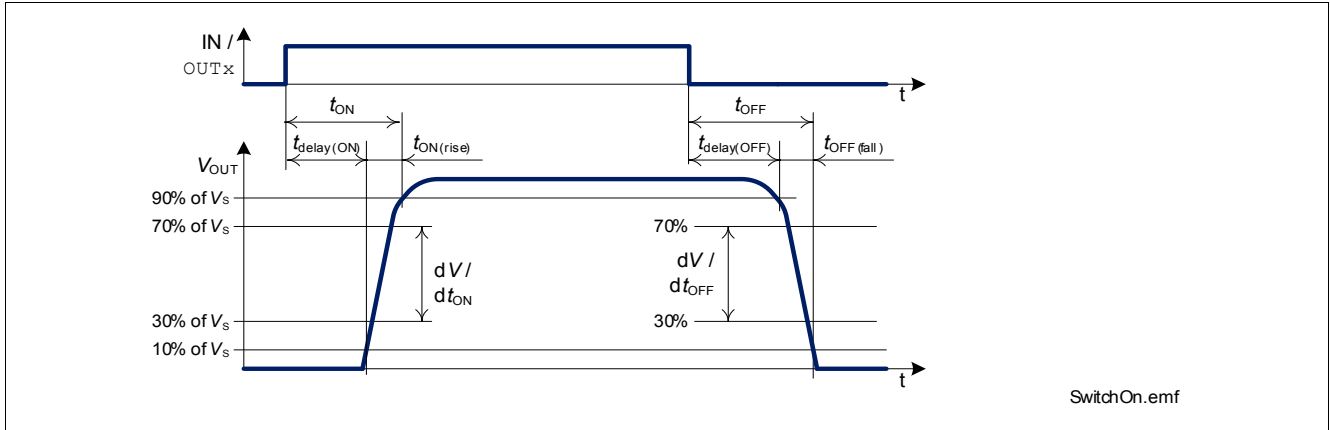When switching resistive loads the following switching times and slew rates can be considered.

Figure 7   Switching a resistive Load

6.3.3 Switching Inductive Loads

When switching off inductive loads with high-side switches, the voltage V_{OUT} drops below ground potential, because the inductance intends to continue driving the current. To prevent the destruction of the device due to high voltages, there is a voltage clamp mechanism implemented, which limits that negative output voltage to a certain level ($V_{DS(CL)}$ (**6.6.2**)). See **Figure 6** for details. The device provides SmartClamp functionality. To increase the energy capability, the clamp voltage $V_{DS(CL)}$ increases with the junction temperature T_j and load current I_L. Please refer also to **Section 7.7**. When switching inductive loads, it has to be ensured that the clamp mechanism of the device is not activated.

6.3.4 Switching high inrush loads

When switching loads with high inrush currents like e.g. high capacitive loads, it has to be ensured that in normal operating range the maximum load current is below the current trip level of the device. If the current trip level is touched, the device would operate under fault conditions that are considered as outside normal operating range. In this case absolute maximum ratings are exceeded (see **4.1.8**). Please refer to **Section 4** and **Section 7** for further information.

6.4 Inverse Current Behavior

During inverse currents ($V_{OUT} > V_S$) the affected channel stays in ON- or in OFF-state. Furthermore, during applied inverse currents no ERR-flag is set.

The functionality of unaffected channels is not influenced by inverse currents applied to other channels (except effects due to junction temperature increase). Influences on the diagnostic function of unaffected channels are possible only for the current sense ratio, please refer to $\Delta k_{ILIS(IC)}$ (**8.5.3**).

Note: No protection mechanism like temperature protection or current protection is active during applied inverse currents. Inverse currents cause power losses inside the DMOS, which increase the overall device temperature, which could lead to a switch off of the unaffected channels due to over temperature.

6.5 External Driver Control

Two external smart power drivers can be driven by the SPOC - BTS5482SF via the external driver control block. For each external driver there are two control outputs available: one output for controlling the input (EDOx) and one output for diagnosis enable input (EDDx). The current sense output of the external smart power drivers can be connected to the IS pin. For details please refer to **Figure 31**.

The external driver outputs can be used only with applied V_{DD} voltage. The external driver outputs are internally pulled down. The external drivers can be activated via SPI-bits `OUTH.OUT4` and `OUTH.OUT5` or via the input pin IN3 in assigned drive mode. The external drivers' diagnostic enable signals can be activated via the SPI register `DCR.MUX`. For being compliant to PROFET+ diagnostic functions, it is possible to configure pin EDD0 as DEN and EDD1 as DSEL. Therefore, the bit `OUTH.PRO+` needs to be set. The DSEL will be set in accordance to the multiplexer setting `DCR.MUX`.

Table 3   PROFET+ Compliancy

MUX Setting DCR.MUX	EDD0 used as DEN	EDD1 used as DSEL
100_b	1	0
101_b	1	1

Note: The usable duty cycle range and diagnostic timings for the external drivers depend on the external driver's characteristics.

6.6 Electrical Characteristics

Electrical Characteristics Power Stages

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Output Characteristics							
6.6.1	On-state resistance	$R_{DS(ON)}$				mΩ	
	channel 0, 1						I_L = 7.5 A
			–	4	–		[1] T_j = 25 °C
			–	6	8.5		T_j = 150 °C
	channel 2, 3						`HWCR.LEDn = 0`
							I_L = 2.6 A
			–	15	–		[1] T_j = 25 °C
			–	21	28		T_j = 150 °C
							`HWCR.LEDn = 1`
							I_L = 0.6 A
			–	45	–		[1] T_j = 25 °C
			–	70	100		T_j = 150 °C
6.6.2	Output clamp	$V_{DS(CL)}$				V	
	channel 0, 1		32	–	54		T_j = 25 °C
							I_L = 20 mA
			40	–	55		[1] T_j = 150 °C
							I_L = 6 A
	channel 2, 3		32	–	54		T_j = 25 °C
							I_L = 20 mA
			40	–	55		[1] T_j = 150 °C
							I_L = 2 A
6.6.3	Output leakage current per channel in stand-by	$I_{L(OFFSTB)}$				µA	`OUTL.OUTn = 0` `DCR.MUX = 111`
	channel 0, 1		–	–	2		T_j = 25 °C
			–	–	10		[1] T_j = 85 °C
			–	–	50		[1] T_j = 105 °C
	channel 2, 3		–	–	1		T_j = 25 °C
			–	–	4		[1] T_j = 85 °C
			–	–	20		[1] T_j = 105 °C
6.6.4	Output leakage current per channel in idle mode	$I_{L(OFFidle)}$				µA	`OUTL.OUTn = 0` `DCR.MUX ≠ 111`
	channel 0, 1		–	–	60		[1] T_j = 85 °C
			–	–	80		[1] T_j = 105 °C
			–	–	530		T_j = 150 °C
	channel 2, 3		–	–	45		[1] T_j = 85 °C
			–	–	50		[1] T_j = 105 °C
			–	–	230		T_j = 150 °C

Electrical Characteristics Power Stages (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
6.6.5	Inverse current capability per channel channel 0, 1 channel 2, 3	$-I_{L(IC)}$	 6 2	 – –	 – –	A	[1] No influences on switching functionality of unaffected channels, k_{ILIS} influence according $\Delta k_{ILIS(IC)}$ (**8.5.3**)
Input Characteristics							
6.6.6	L-input level	$V_{IN(L)}$	0	–	0.8	V	–
6.6.7	H-input level	$V_{IN(H)}$	1.8	–	5.5	V	–
6.6.8	L-input current	$I_{IN(L)}$	3	8	20	µA	[1] V_{IN} = 0.6 V `DCR.MUX` ≠ `111`
6.6.9	H-input current	$I_{IN(H)}$	10	40	80	µA	V_{IN} = 5 V

Electrical Characteristics Power Stages (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Timings							
6.6.10	Turn-ON delay to 10% V_S	$t_{delay(ON)}$				µs	[1] V_S = 13.5 V
	channel 0, 1		–	35	–		–
	channel 2, 3		–	25	–		`HWCR.LEDn = 0`
			–	8	–		`HWCR.LEDn = 1`
6.6.11	Turn-OFF delay to 90% V_S	$t_{delay(OFF)}$				µs	[1] V_S = 13.5 V
	channel 0, 1		–	45	–		–
	channel 2, 3		–	30	–		`HWCR.LEDn = 0`
			–	10	–		`HWCR.LEDn = 1`
6.6.12	Turn-ON time to 90% V_S including turn-ON delay	t_{ON}				µs	V_S = 13.5 V `DCR.MUX ≠ 111`
	channel 0, 1		–	–	100		R_L = 2.2 Ω
	channel 2, 3		–	–	100		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	–	50		`HWCR.LEDn = 1` R_L = 33 Ω
6.6.13	Turn-OFF time to 10% V_S including turn-OFF delay	t_{OFF}				µs	V_S = 13.5 V
	channel 0, 1		–	–	150		R_L = 2.2 Ω
	channel 2, 3		–	–	110		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	–	50		`HWCR.LEDn = 1` R_L = 33 Ω
6.6.14	Turn-ON rise time from 10% to 90% V_S	$t_{ON(rise)}$				µs	V_S = 13.5 V `DCR.MUX ≠ 111`
	channel 0, 1		–	–	45		R_L = 2.2 Ω
	channel 2, 3		–	–	40		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	–	11		`HWCR.LEDn = 1` R_L = 33 Ω
6.6.15	Turn-OFF fall time from 90% to 10% V_S	$t_{OFF(fall)}$				µs	V_S = 13.5 V
	channel 0, 1		–	–	45		R_L = 2.2 Ω
	channel 2, 3		–	–	40		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	–	11		`HWCR.LEDn = 1` R_L = 33 Ω

Electrical Characteristics Power Stages (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
6.6.16	Turn-ON/OFF matching	$\|t_{ON} - t_{OFF}\|$				µs	V_S = 13.5 V
	channel 0, 1		–	–	90		R_L = 2.2 Ω
	channel 2, 3		–	–	70		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	–	50		`HWCR.LEDn = 1` R_L = 33 Ω
6.6.17	Turn-ON slew rate 30% to 70% V_S	dV/dt_{ON}				V/µs	V_S = 13.5 V
	channel 0, 1		–	0.7	2.0		R_L = 2.2 Ω
	channel 2, 3		–	0.9	2.5		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	2.5	6.0		`HWCR.LEDn = 1` R_L = 33 Ω
6.6.18	Turn-OFF slew rate 70% to 30% V_S	$-dV/dt_{OFF}$				V/µs	V_S = 13.5 V
	channel 0, 1		–	0.7	2.0		R_L = 2.2 Ω
	channel 2, 3		–	0.9	2.5		`HWCR.LEDn = 0` R_L = 6.8 Ω
			–	2.5	6.0		`HWCR.LEDn = 1` R_L = 33 Ω
External Driver Control							
6.6.19	L level external driver output voltage	$V_{EDO(L)}$	0	–	0.4	V	I_{EDO} = -0.5 mA
6.6.20	H level external driver output voltage	$V_{EDO(H)}$	V_{DD} - 0.4V	–	V_{DD}	V	I_{EDO} = 0.5 mA V_{DD} = 4.3 V
6.6.21	External driver output enable time	$t_{EDO(en)}$	–	–	4	µs	[1] C_L = 20 pF
6.6.22	External driver output disable time	$t_{EDO(dis)}$	–	–	4	µs	[1] C_L = 20 pF
6.6.23	L level external driver diagnosis enable voltage	$V_{EDD(L)}$	0	–	0.4	V	I_{EDD} = -0.5 mA
6.6.24	H level external driver diagnosis enable voltage	$V_{EDD(H)}$	V_{DD} - 0.4V	–	V_{DD}	V	I_{EDD} = 0.5 mA V_{DD} = 4.3 V
6.6.25	External driver diagnosis enable enable time	$t_{EDD(en)}$	–	–	4	µs	[1] C_L = 20 pF
6.6.26	External driver diagnosis enable disable time	$t_{EDD(dis)}$	–	–	4	µs	[1] C_L = 20 pF

1) Not subject to production test, specified by design.

7 Protection Functions

SPOC - BTS5482SF provides embedded protective functions, which are designed to prevent IC destruction under fault conditions described in this data sheet. Fault conditions are considered as "outside" normal operating range. Protective functions are neither designed for continuous nor for repetitive operation. To provide high switching capability and robustness, the device is managed by a state machine (**Figure 8**).
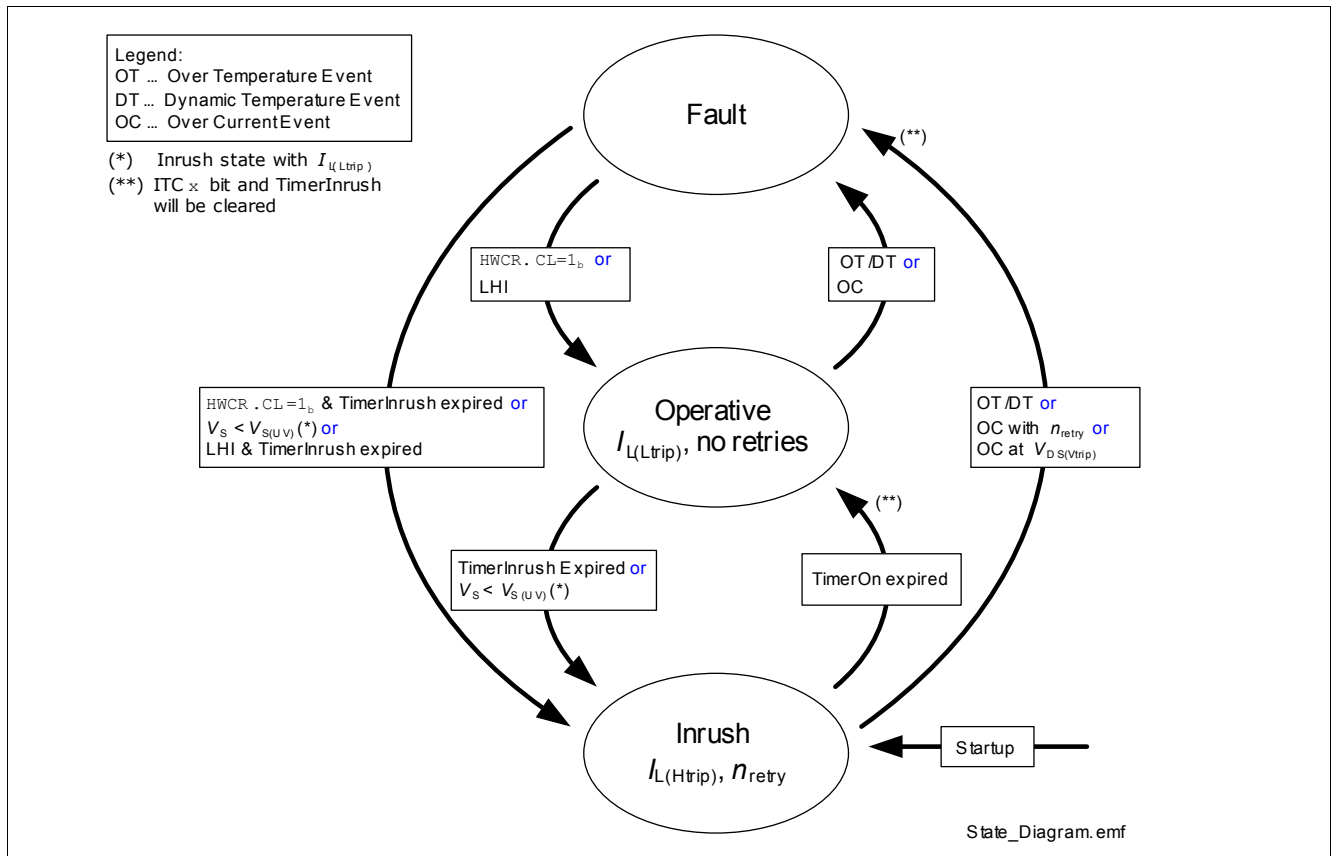

Legend:
OT … Over Temperature Event
DT … Dynamic Temperature Event
OC … Over Current Event

(*) Inrush state with $I_{L(Ltrip)}$
(**) ITC$_x$ bit and TimerInrush will be cleared

Fault

HWCR.CL=1$_b$ or LHI

OT/DT or OC

HWCR.CL=1$_b$ & TimerInrush expired or $V_S < V_{S(UV)}$ (*) or LHI & TimerInrush expired

Operative $I_{L(Ltrip)}$, no retries

OT/DT or OC with n_{retry} or OC at $V_{DS(Vtrip)}$

TimerInrush Expired or $V_S < V_{S(UV)}$ (*)

TimerOn expired

Inrush $I_{L(Htrip)}$, n_{retry}

Startup

State_Diagram.emf

Figure 8   BTS5482SF state diagram

Each internal channel of BTS5482SF has its own state machine to manage the protection mechanisms. Device is starting-up in Inrush state and depending on different conditions it will change to Operative state (normal condition) or to Fault state (overload condition).

7.1 Inrush State

After start-up the device enters Inrush state providing high current trip level $I_{L(Htrip)}$ (**7.10.1**) with a limited number of retries (see **Figure 11**). After the respective channel is in ON-state for $t > t_{delay(Ltrip)}$ (**7.10.2**), the channel changes to Operative state (see **Chapter 7.2**). In case the channels are driven in PWM (pulse width modulation) the ON-time is cumulated until $t_{delay(Ltrip)}$ is reached. For a detailed description of the timers see **Chapter 7.4**. If a latch off condition occurs, the device will change to Fault state (see **Chapter 7.3**).

7.1.1 Over Current Protection in Inrush State

The maximum load current I_L is switched off in case of exceeding the over current trip level $I_{L(Htrip)}$ by the device itself. Depending on the total short circuit impedance higher current over shoots may occur. A limited auto-restart function is implemented. Please refer to following figures for details.
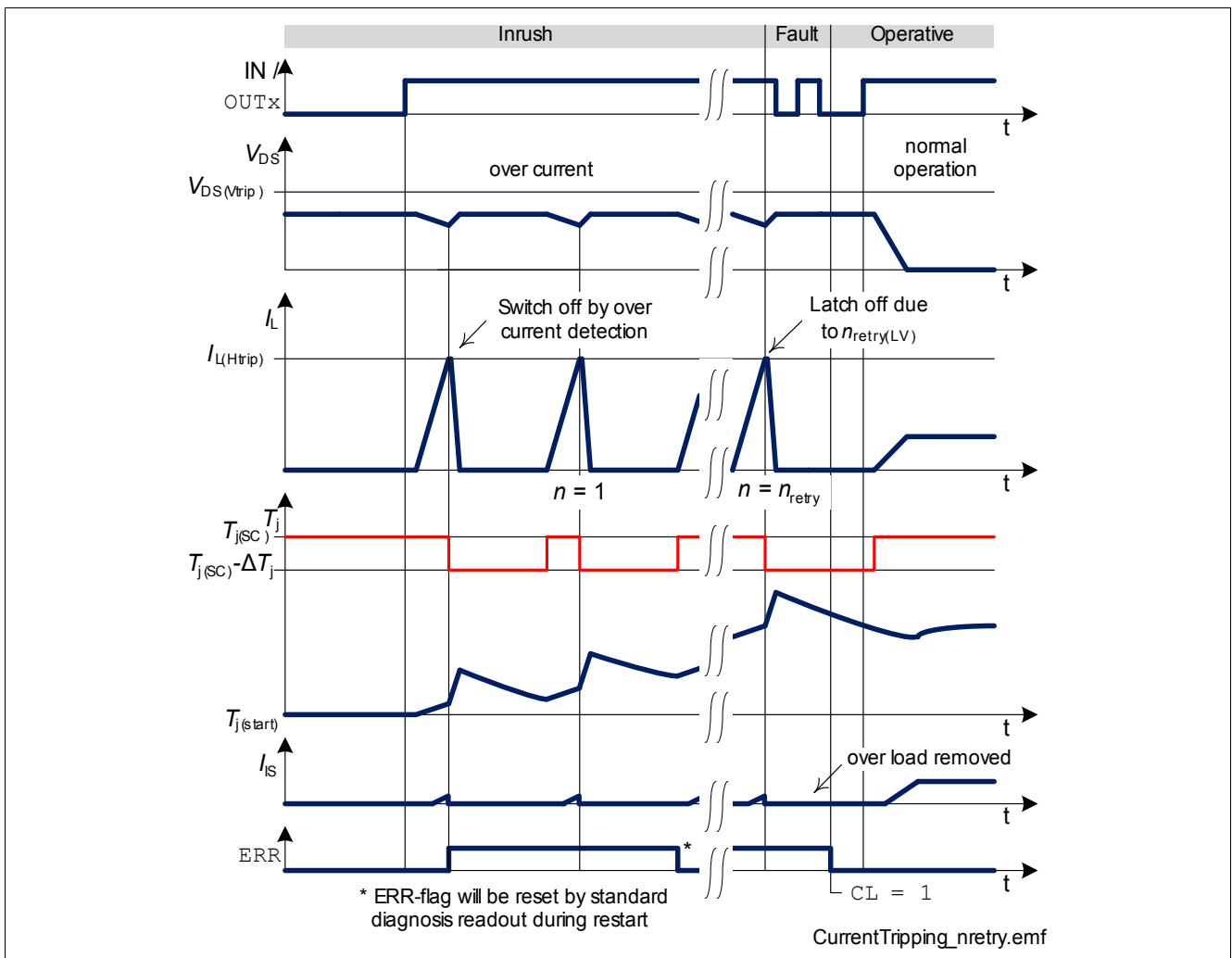
Figure 9 **Over current protection with latch due to reaching maximum number of retries n_retry**

In PWM operation the number of retries is cumulated over PWM cycles until n_retry is reached. Please refer to **Figure 10** for a more detailed view.
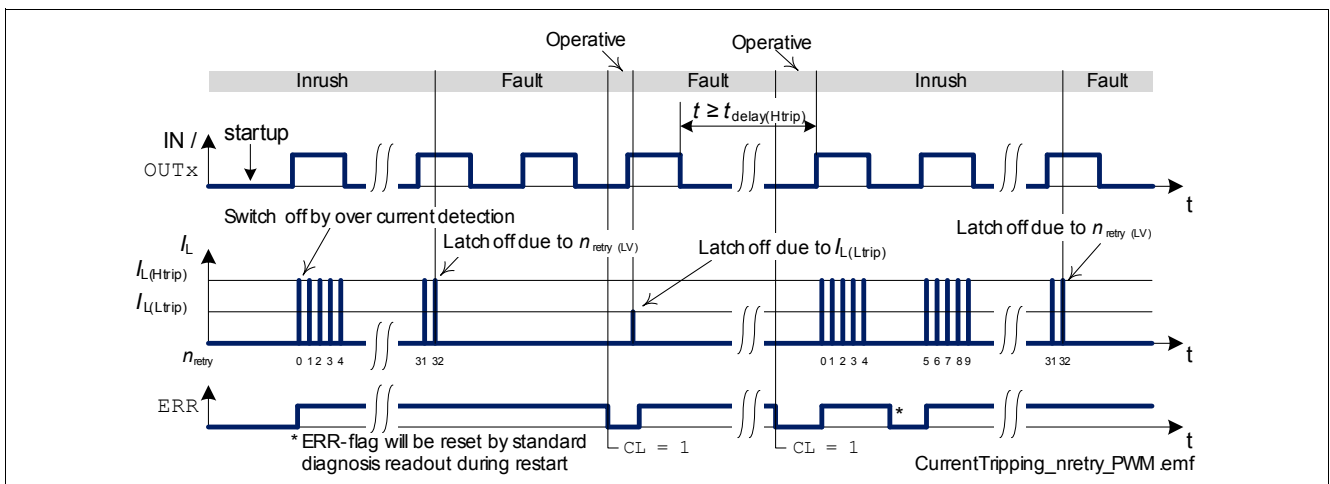

Figure 10 **Over current protection with latch due to reaching maximum number of retries n_retry in PWM**

The ERR-flag will be set during over current shut down. It can be reset by reading the ERR-flag, unless Fault state is reached by exceeding n_{retry}. It will be set again with the next over current event. See figures above.

The number of restarts n_{retry} is depending on the V_{DS} voltage according to the following figure and **Chapter 7.1.2**.
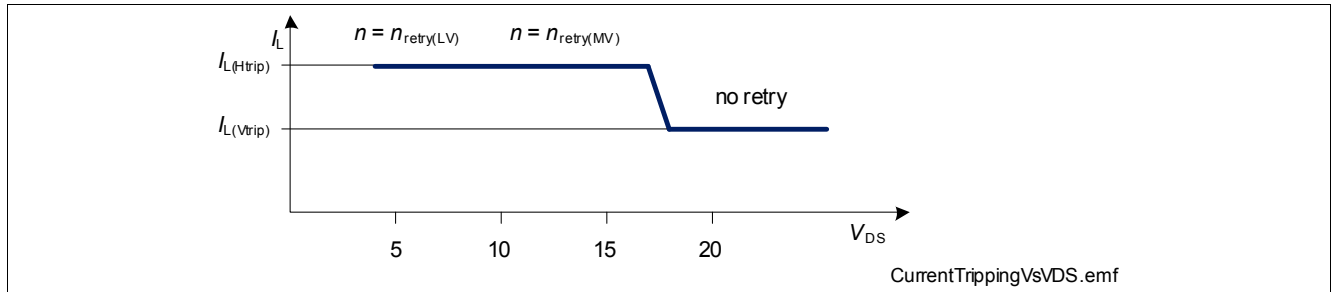

Figure 11   Number of retries and trip levels dependent of V_{DS}

The retry latch is cleared by SPI command `HWCR.CL = 1`$_{b}$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_{b}$. To prevent degradation of the device, channel is restarting in Operative state (**Chapter 7.2**).

7.1.2   Over Current Protection at high V_{DS}

The SPOC - BTS5482SF provides an over current protection at high V_{DS} (**7.10.6**). For $V_{DS} > V_{DS(Vtrip)}$ and $I_L > I_{L(Vtrip)}$ during turn-on the channel switches off and latches immediately. For details please refer to parameter $I_{L(VTRIP)}$ (**7.10.5**).

The current trip level $I_{L(Vtrip)}$ is below the current trip level $I_{L(Htrip)}$ at $V_{DS} = 7V$.

The over current latch is cleared by SPI command `HWCR.CL = 1`$_{b}$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_{b}$. To prevent degradation of the device it is recommended to wait $t_{delay(CL)}$ (**4.1.10**) until resetting the latch and restarting in Operative state.
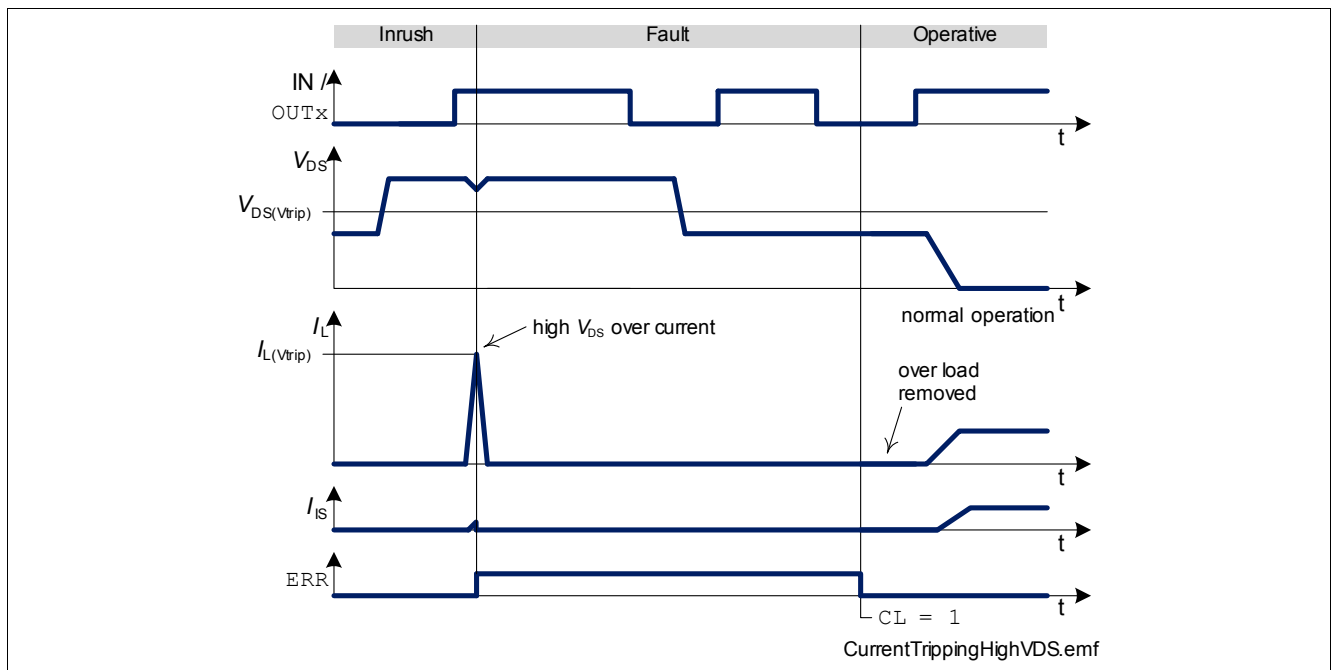

Figure 12   Over current protection in case of high V_{DS} voltages

7.1.3 Over Temperature Protection

Each channel has its own temperature sensor. If the temperature at the channel exceeds the thermal shutdown temperature $T_{j(SC)}$, the channel will switch off and latch to prevent destruction (also in case of $V_{DD} = 0V$). After an overcurrent event the threshold $T_{j(SC)}$ will be decreased by the thermal hysteresis ΔT_j (**7.10.11**). In order to reactivate the channel, the temperature must drop by at least the thermal hysteresis ΔT_j and the over temperature latch must be cleared by SPI command `HWCR.CL = 1`$_b$. When channel restarts the overtemperature threshold is reset to $T_{j(SC)}$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_b$.To prevent degradation of the device it is recommended to wait $t_{delay(CL)}$ (**4.1.10**) until resetting the latch and restarting in Operative state.
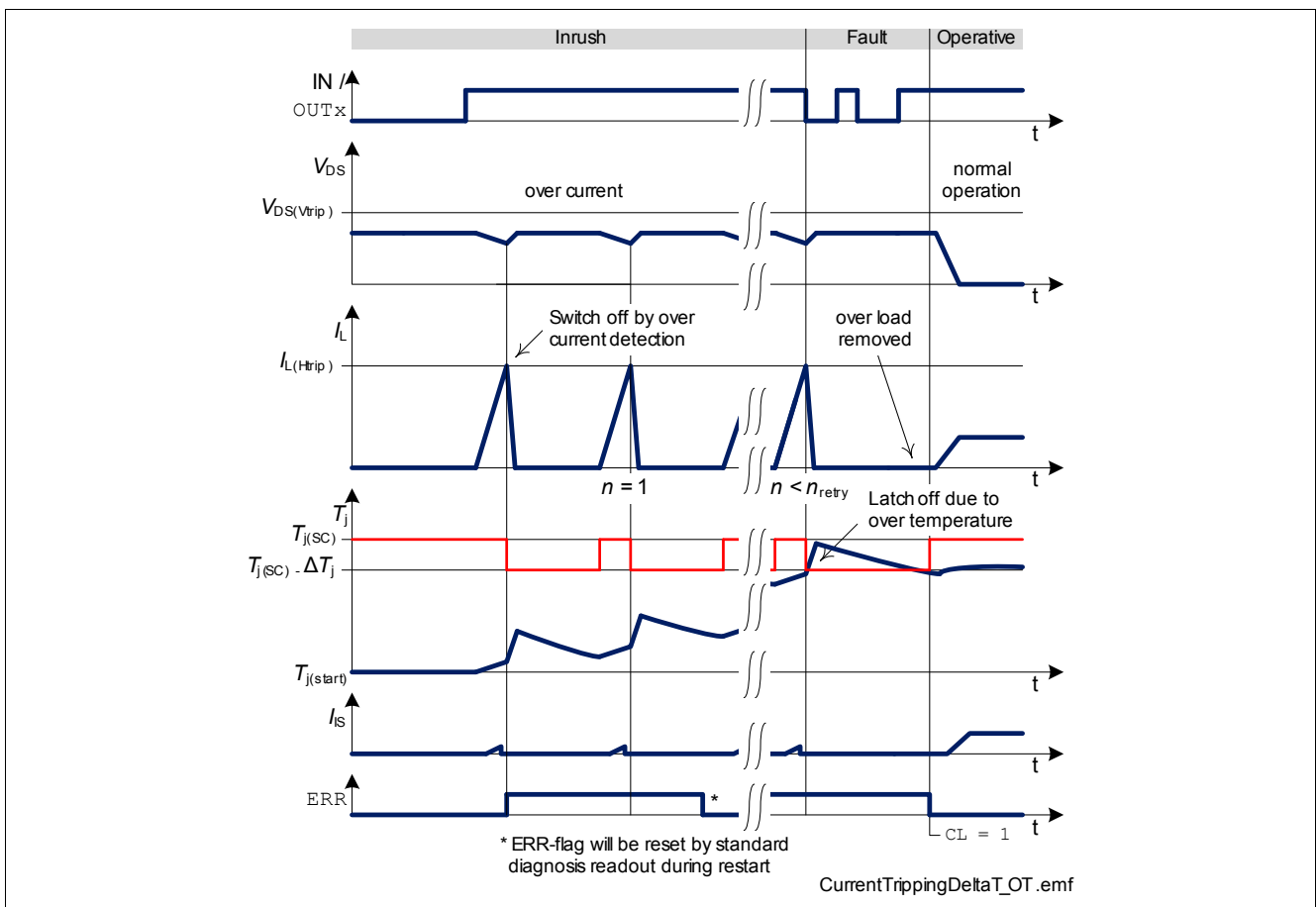

Figure 13   Over current protection with latch due to reaching over temperature $T_{j(SC)}$
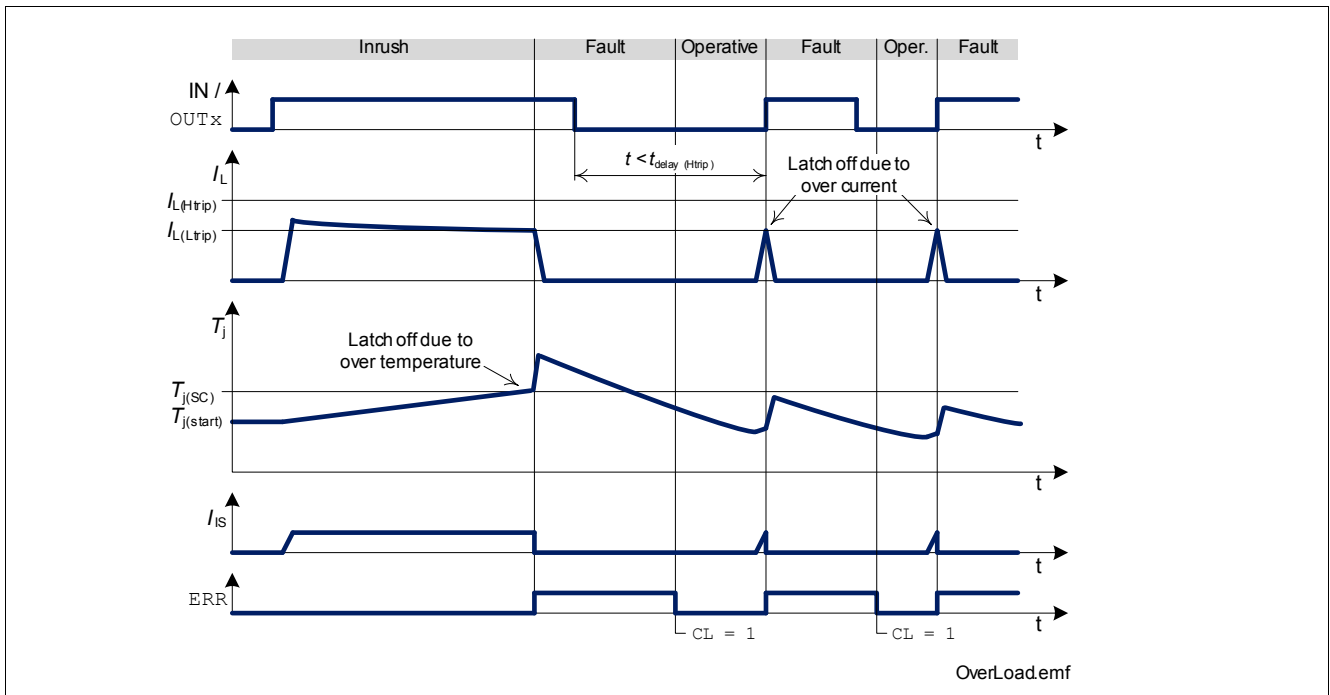
Figure 14   Shut Down by Over Temperature

7.1.4 Dynamic Temperature Protection

Additionally, each channel has its own dynamic temperature protection to improve short circuit robustness when channels are doing automatic retries. The dynamic temperature protection will check the junction temperature of each channel after an overcurrent event. When the junction temperature (T_j) compared to the temperature of the reference sensor (T_{Ref}) is below the dynamic temperature threshold $\Delta T_{j(res)}$ the channel is restarting (t_1 in **Figure 15**). As soon as $T_j > T_{Ref} + \Delta T_{j(res)}$ the channel will be latched off and the ERR-flag will be set (t_2 in **Figure 15**). The latch is cleared by SPI command `HWCR.CL = 1`$_b$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_b$. To prevent degradation of the device it is recommended to wait $t_{delay(CL)}$ (**4.1.10**) until resetting the latch and restarting in Operative state.
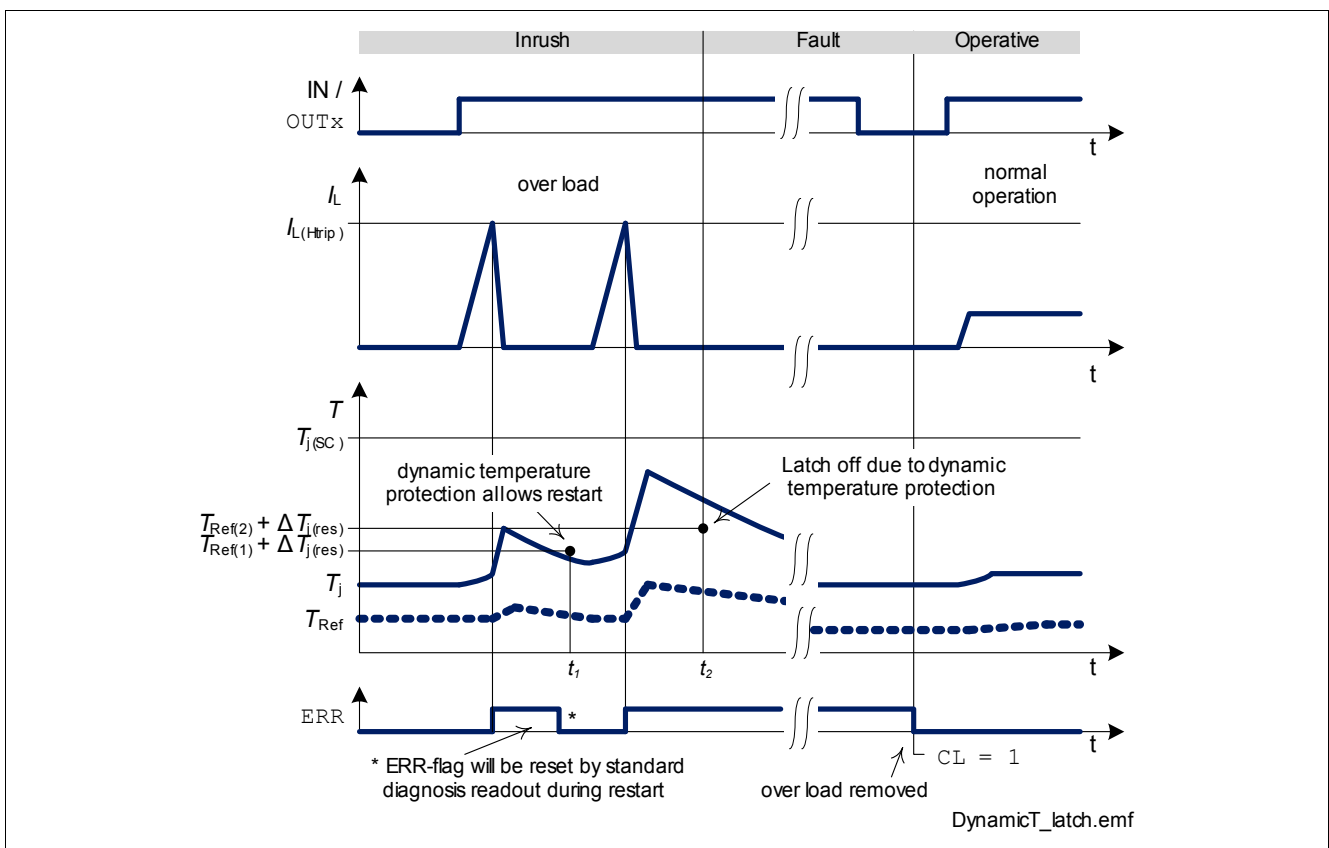

Figure 15 Dynamic Temperature Protection with latch

7.2 Operative State

In this state the device allows only low current trip level $I_{L(Ltrip)}$ (**7.10.4**). Channel switches off and latches immediately in case the trip level is reached. To change from Operative State to Inrush State the respective channel has to be in OFF-state for $t_{delay(Htrip)}$. For a detailed description see **Chapter 7.4**.

7.2.1 Over Current Protection in Operative State

In case of a short circuit to GND event with $I_L > I_{L(Ltrip)}$ (**7.10.4**), the channel is latched off immediately and it will change to Fault State. For more details, please refer to the figure **Figure 16**.

The over current latch is cleared by SPI command `HWCR.CL = 1`$_b$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_b$. Depending on the state of the TimerInrush ($t_{delay(Htrip)}$) the device will either restart in Inrush or Operative state.
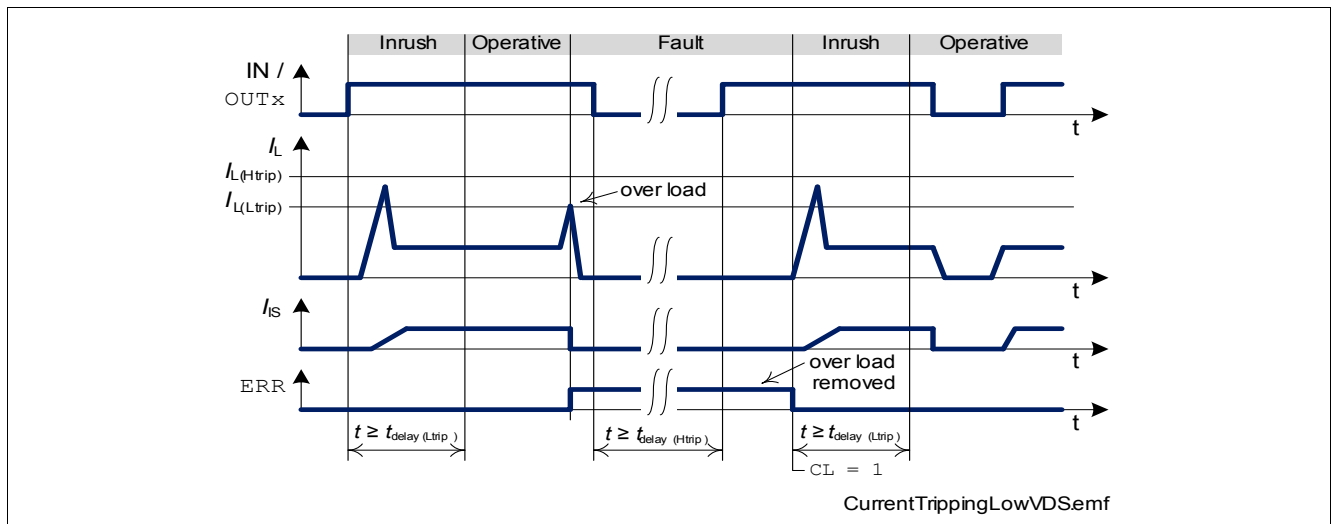

Figure 16   Shut Down by Over Current in Operative State

7.2.2 Over Temperature Protection in Operative State

If the junction temperature exceeds the thermal shutdown temperature $T_{j(SC)}$, the channel will switch off and latch to prevent destruction (also in case of $V_{DD} = 0V$). In order to reactivate the channel, the temperature must drop below $T_{j(SC)}$ and the over temperature latch must be cleared by SPI command `HWCR.CL = 1`$_b$. If the input pin or the bit in the SPI register `OUTL` is still set, the channel will be turned-on immediately after the command `HWCR.CL = 1`$_b$. To prevent degradation of the device it is recommended to wait $t_{delay(CL)}$ (**4.1.10**) until resetting the latch and restarting in Operative state. See **Figure 14** for a detailed view.

7.2.3 Dynamic Temperature Protection in Operative State

In this State the dynamic temperature protection is not needed to protect the device. For an improved EMI performance this function is disabled.

7.3 Fault State

In this State the respective channel is in a latched off condition due to an overload event occurred in Inrush or Operative State. To reactivate the channel the command `HWCR.CL = 1`$_b$ has to be sent over SPI. After the clear latch command the channel will change to Operative State. To restart in Inrush State the respective channel has to be OFF for $t > t_{delay(Htrip)}$. See **Figure 16** and **Chapter 7.4** for further details.

7.4 Timers and n_{retry} counter

Each state machine uses two different timers (TimerOn and TimerInrush) to control the state transitions. A counter is used to limit the maximum number of automatic restarts (n_{retry}).

The TimerOn controls the automatic state transition from Inrush to Operative. As soon the channel is activated in Inrush State (SPI or IN) the TimerOn (**7.10.2**) is running. The behavior of this timer is shown in the table below.

Table 4   TimerOn behavior

TimerOn	OC / DT / OT = 0		OC / DT / OT = 1	
	ON = 0	ON = 1	ON = 0	ON = 1
Inrush State	hold	running	n.a.	reset
Operative / Fault State	reset	reset	reset	reset

In case of an overload event the TimerOn is reset to provide a higher inrush capability. **Figure 17** shows the TimerOn behavior when switching on a high inrush load. After the last overcurrent event the TimerOn is restarted. When the timer expires ($t > t_{delay(Ltrip)}$) the Operative State is entered.
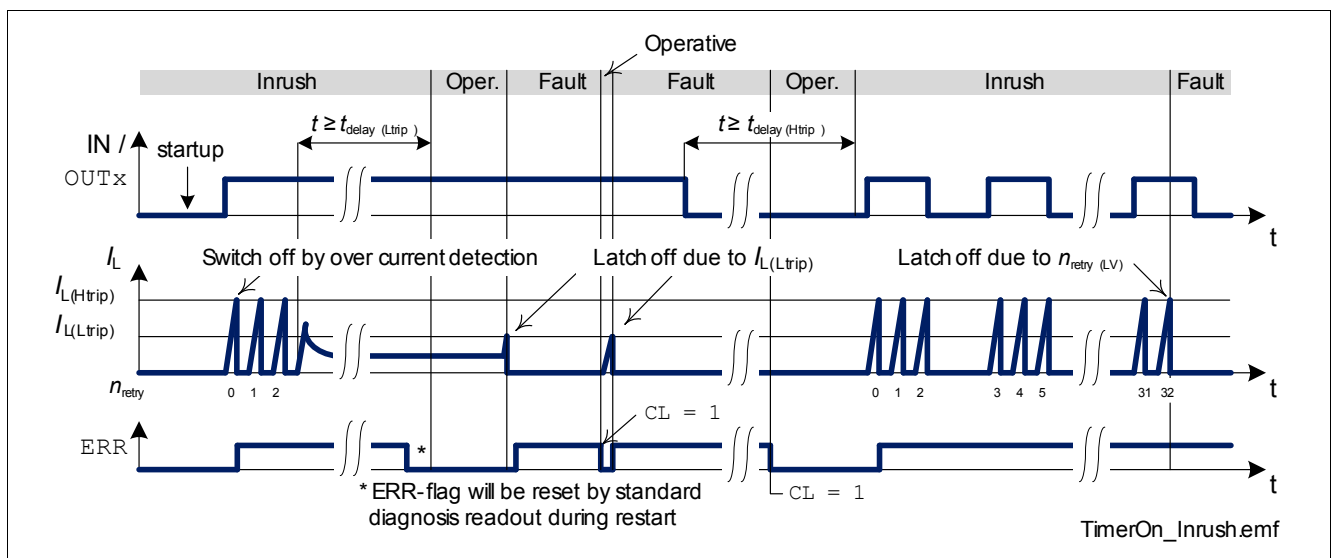

Figure 17   Timer-ON behavior with high inrush load

In case of PWM operation the TimerOn is cumulating the ON-state time of the channel. As soon as $\Sigma t_{on} > t_{delay(Ltrip)}$ the channel is entering Operative State. **Figure 18** shows a high ohmic short circuit in PWM operation, where the load current does not reach $I_{L(Htrip)}$. When $\Sigma t_{on} > t_{delay(Ltrip)}$ the Operative state is entered. Due to the lower current trip level $I_{L(Ltrip)}$ the channel is latched off and the Fault State is entered.
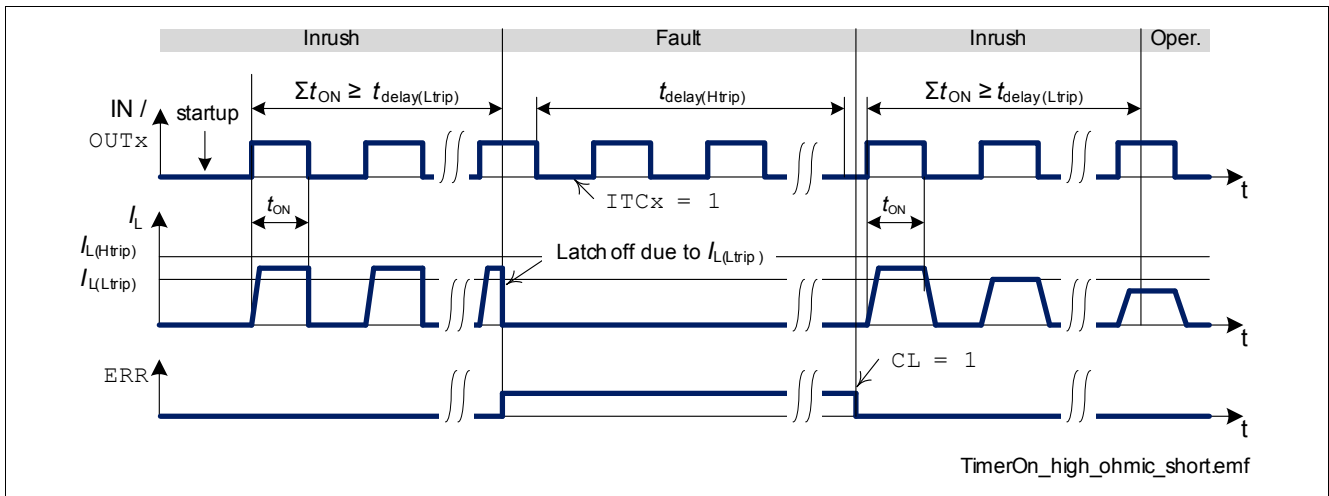
Figure 18   TimerOn and TimerInrush behavior in high ohmic short condition

To reactivate the channel in Operative State the command `HWCR.CL = 1`$_b$ has to be sent. In case the device needs to be restarted in Inrush State the TimerInrush has to be expired. See **Figure 18**. **Table 5** shows the behavior of the TimerInrush in the different states of the state machine.

Table 5   TimerInrush

TimerInrush	ITCx = 0		ITCx = 1	
	ON = 0	ON = 1	ON = 0	ON = 1
Inrush State	running	reset	running	reset
Operative / Fault State	running	reset	running	running

TimerInrush is needed to change from Operative or Fault to Inrush state. In standard configuration (ITCx = 0) the TimerInrush is only running when the respective channel is deactivated. To provide some more flexibility in software, it is possible to have the TimerInrush running when the channel is activated or in PWM operation (ITCx = 1). When Limp Home mode is activated the TimerInrush is running independent of the state of the channels. The bit ITCx and TimerInrush are reset at every state transition from Inrush to Operative or Inrush to Fault. See **Figure 8**.

To limit the number of automatic retries each channel has its own retry counter. As soon the counter reaches the maximum value (n_{retry}), the device changes to Fault state. The value of this counter is frozen when the channel is switched off for $t < t_{delay(Htrip)}$. The behavior of this counter is shown in **Table 6**.

Table 6 n_{retry} counter

n_{retry} counter	TimerInrush not expired		TimerInrush expired	
	ON = 0	ON = 1	ON = 0	ON = 1
Inrush State	frozen	running	reset	n.a.
Operative / Fault State	reset	reset	reset	reset

7.5 Undervoltage restarts

To increase the device robustness at low V_S condition, the device provides V_S monitoring functionality. In case $V_S < V_{S(mon)}$ the load current trip level is reduced to $I_{L(Ltrip)}$. In case $I_L > I_{L(Ltrip)}$ the channel will restart until the maximum number of retries ($n_{retry(LV)}$) is reached. It has to be ensured that V_S does not drop below $V_{S(ext)}$, otherwise the undervoltage shutdown could be entered (see **5.3.3**). If this occurs before current trip level is reached, the protection mechanisms are reset and the channels are restarting with low current trip level $I_{L(Ltrip)}$. If this occurs after over current detection (e.g. due to oscillations on battery) the protection mechanisms are reset and the channels are restarting with high current trip level $I_{L(Htrip)}$. To mitigate oscillations on the battery a good filtering on VS is recommended.
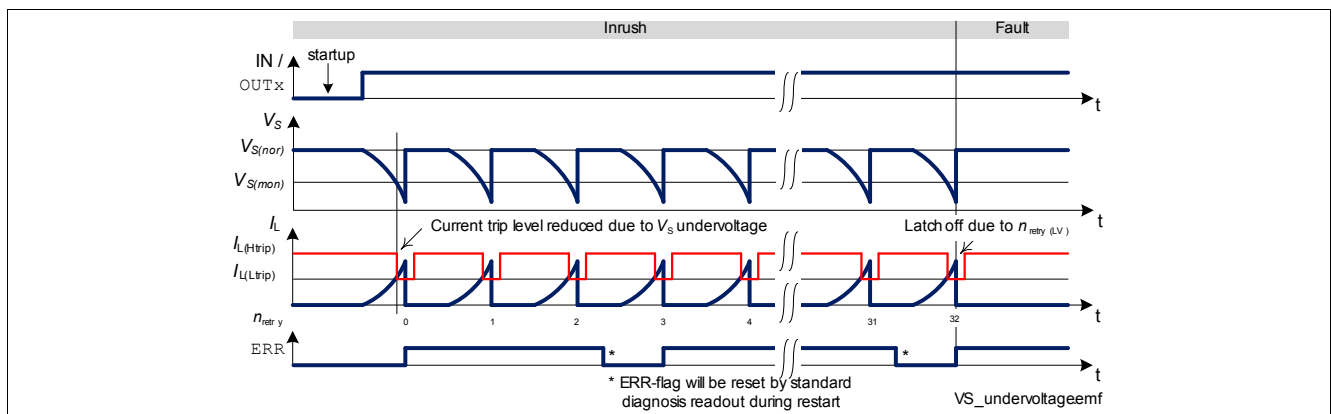

Figure 19   Behavior of current trip level in VS undervoltage condition

7.6 Reverse Polarity Protection

To reduce power losses during reverse polarity Reversave^{TM} functionality is implemented for all internal channels. They are turned-on to almost forward condition in reverse polarity condition, see parameter $R_{DS(REV)}$. In reverse polarity mode, power dissipation is caused by the reverse ON-state resistance $R_{DS(REV)}$ of each channel as well as each ESD diode of the logic pins. The reverse current through the channels has to be limited by the connected loads. The current through the ground pin, sense pin IS, the logic power supply pin VDD, the SPI pins, input pins, external driver pins and the limp home input pin has to be limited as well (please refer to the maximum ratings listed on **Page 10**).

Note: No protection mechanism like temperature protection or current protection is active during reverse polarity.

7.7 Over Voltage Protection

In the case of supply voltages between $V_{S(SC)max}$ and $V_{S(CL)}$ the output transistors are still operational and follow the input or the OUTL register. Parameters are not warranted and lifetime is reduced compared to normal mode.

In addition to the output clamp for inductive loads as described in **Section 6.3**, there is a clamp mechanism available for over voltage protection of the internal circuits.

7.8 Loss of Ground

In case of complete loss of the device ground connections, but connected load ground, the SPOC - BTS5482SF securely changes to or stays in OFF-state.

7.9 Loss of V_S

In case of loss of V_S connection in ON-state, all inductances of the loads have to be demagnetized through the ground connection or through an additional path from VS to GND. For example, a suppressor diode is recommended between VS and GND.

7.10 Electrical Characteristics

Electrical Characteristics Protection Functions

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Over Current Protection							
7.10.1	Load current trip level	$I_{L(Htrip)}$				A	V_{DS} < 7 V
	channel 0, 1		71	–	120		T_j = -40 °C
			–	90	–		[1] T_j = 25 °C
			67	–	100		T_j = 150 °C
	channel 2, 3						HWCR.LEDn = 0
			29	–	44		T_j = -40 °C
			–	30	–		[1] T_j = 25 °C
			23	–	39		T_j = 150 °C
							HWCR.LEDn = 1
			7	–	12		T_j = -40 °C
			–	8.5	–		[1] T_j = 25 °C
			5.5	–	11		T_j = 150 °C
7.10.2	Operative State activation time	$t_{delay(Ltrip)}$	7	10	14	ms	[1]
7.10.3	Inrush State re-activation time	$t_{delay(Htrip)}$	–	160	250	ms	[1]
7.10.4	Load current trip level after $t_{delay(Ltrip)}$	$I_{L(Ltrip)}$				A	
	channel 0, 1		40	–	78		T_j = -40 °C
			35	–	70		T_j = 150 °C
	channel 2, 3						HWCR.LEDn = 0
			17	–	35		T_j = -40 °C
			15.5	–	30		T_j = 150 °C
							HWCR.LEDn = 1
			3.8	–	9		T_j = -40 °C
			3.8	–	8		T_j = 150 °C
7.10.5	Load current trip level at high V_{DS}	$I_{L(Vtrip)}$				A	[1]
	channel 0, 1		40	–	78		T_j = -40 °C
			35	–	70		T_j = 150 °C
	channel 2, 3						HWCR.LEDn = 0
			17	–	35		T_j = -40 °C
			15.5	–	30		T_j = 150 °C
							HWCR.LEDn = 1
			3.8	–	9		T_j = -40 °C
			3.8	–	8		T_j = 150 °C
7.10.6	Over current tripping at high V_{DS} activation level	$V_{DS(Vtrip)}$	15	20	–	V	[1]
7.10.7	V_S monitoring threshold	$V_{S(mon)}$	–	5.7	–	V	[1]

Electrical Characteristics Protection Functions (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Over Temperature Protection							
7.10.8	Number of automatic retries at over current or dynamic temperature sensor shut down at low V_{DS}	$n_{retry(LV)}$	–	–	32		[1] V_{DS} = 9 V
7.10.9	Number of automatic retries at over current or dynamic temperature sensor shut down at medium V_{DS}	$n_{retry(MV)}$	–	–	8		[1] V_{DS} = 13 V
7.10.10	Thermal shut down temperature	$T_{j(SC)}$	150	180	210	°C	[1]
7.10.11	Thermal hysteresis of thermal shutdown	ΔT_j	–	15	–	K	[1]
7.10.12	Dynamic temperature sensor restart	$\Delta T_{j(res)}$	–	35	–	K	[1]
Reverse Battery							
7.10.13	On-state resistance	$R_{DS(REV)}$				mΩ	[1] V_S = -13.5 V
	channel 0, 1						I_L = -7.5 A
			–	4	–		T_j = 25 °C
			–	6	–		T_j = 150 °C
	channel 2, 3						I_L = -2.6 A
			–	15	–		T_j = 25 °C
			–	21	–		T_j = 150 °C
Over Voltage							
7.10.14	Over voltage protection	$V_{S(CL)}$				V	
	VS to GND		40	60	71		I_{GND} = 5 mA
	channel 0, 1		32	–	54		T_j = 25 °C I_L = 20 mA
			40	–	55		[1] T_j = 150 °C I_L = 6 A
	channel 2, 3		32	–	54		T_j = 25 °C I_L = 20 mA
			40	–	55		[1] T_j = 150 °C I_L = 2 A

1) Not subject to production test, specified by design.

8 Diagnosis

For diagnosis purpose, the SPOC - BTS5482SF provides a current sense signal at pin IS and the diagnosis word via SPI. There is a current sense multiplexer implemented that is controlled via SPI. The sense signal can also be disabled by SPI command. A switch bypass monitor allows to detect a short circuit between the output pin and the battery voltage.

In OFF-state a current source is able to be switched on for a selected channel with the `DCR.CSOL` bit. This allows open load / short circuit detection to V_S in OFF-state. The current value can be configured to a low or a high value by programming the bit `ICR.CSL`. Please refer to parameter $I_{L(OL)}$ (**8.5.16**).

Note: All parameters and functions stated below are valid for the internal channels. The behavior of the current sense of the two external channel is restricted to the behavior of the external drivers.

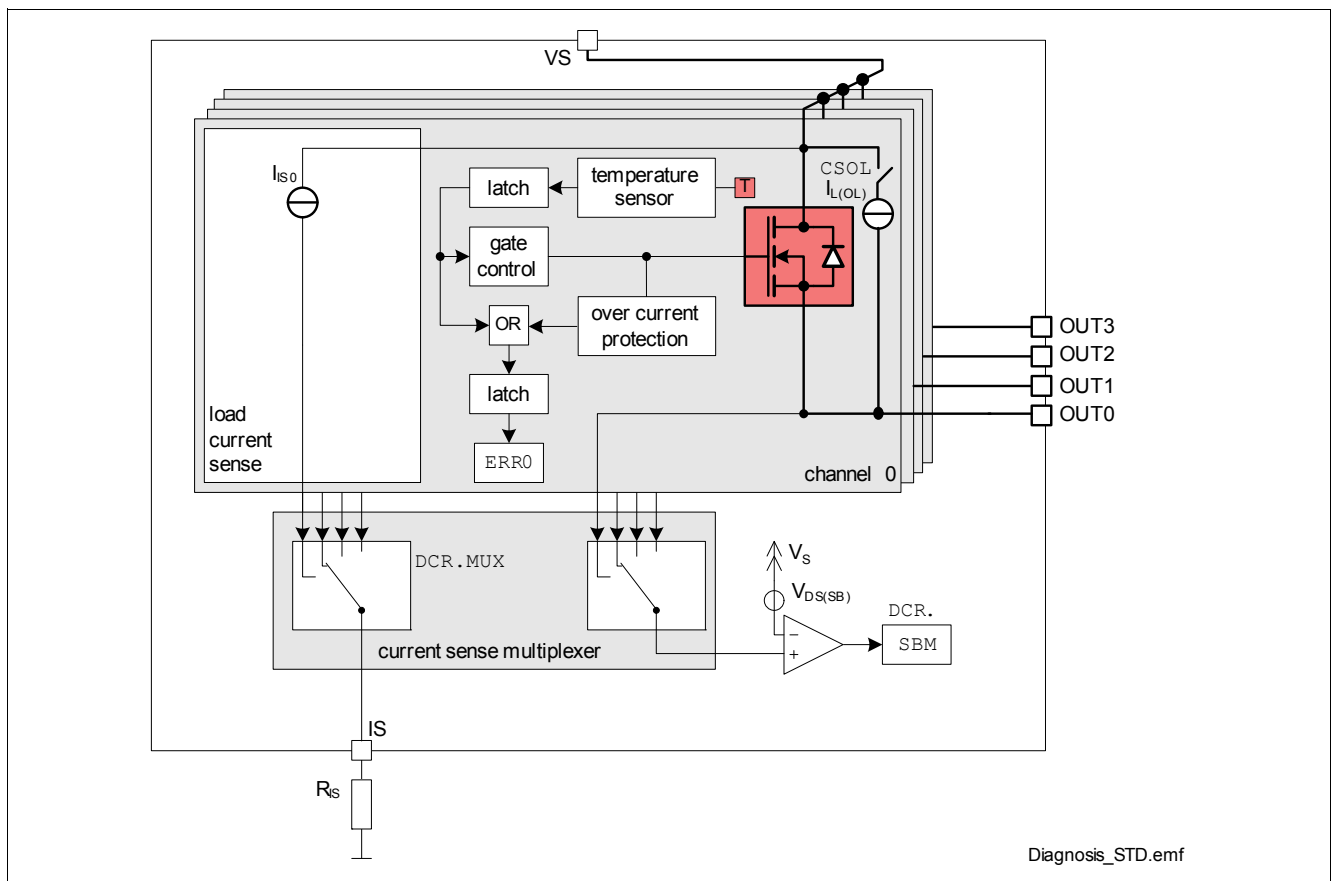Please refer to **Figure 20** for details on diagnosis function:

Figure 20   Block diagram: Diagnosis

SPOC - BTS5482SF

Diagnosis

For diagnosis feedback at different operation modes, please see following table.

Table 7   Operation Modes [1]

Operation Mode	Input Level `OUTL.OUTn`	Output Level V_{OUT}	Current Sense I_{IS}	Error Flag `ERRn`[2]	SBM `DCR.SBM`
Normal Operation (OFF)	L / `0` (OFF-state)	GND	Z	0	1
Short Circuit to GND		GND	Z	0	1
Thermal shut down		Z	Z	0	x
Short Circuit to V_S		V_S	Z	0	0
Open Load		Z	Z	0	0[3]
Inverse Current		> V_S	Z	0	0[4]
Normal Operation (ON)	H / `1` (ON-state)	~ V_S	I_L / k_{ILIS}	0	0
Short Circuit to GND		~ GND	Z	1	1
Dynamic Temperature Sensor shut down		Z	Z	1	x
Over Current shut down		Z	Z	1[5]	x
Thermal shut down		Z	Z	1[6]	x
Short Circuit to V_S		V_S	< I_L / k_{ILIS}	0	0
Open Load		V_S	Z	0	0
Inverse Current		> V_S	Z	0	0

1) L = low level, H = high level, Z = high impedance, potential depends on leakage currents and external circuit x = undefined

2) The error flags are latched until they are transmitted in the standard diagnosis word via SPI

3) If the current sense multiplexer is set to Channel 0 to 3 and `DCR.CSOL` bit set

4) If the current sense multiplexer is set to Channel 0 to 3

5) The over current latch off flag is set latched and can be cleared by SPI command `HWCR.CL`

6) The over temperature flag is set latched and can be cleared by SPI command `HWCR.CL`

8.1   Diagnosis Word at SPI

The standard diagnosis at the SPI interface provides information about each channel. The error flags, an OR combination of the over temperature flags and the over load monitoring signals are provided in the SPI standard diagnosis bits `ERRn`.

The over load monitoring signals are latched in the error flags and cleared each time the standard diagnosis is transmitted via SPI. In detail, they are cleared between the second and third raising edge of the SCLK signal.

The over temperature flags, which cause an overheated channel to latch off, are latched directly at the gate control block. The over current flags, which cause a channel driving a too high current to switch off, are latched like the over temperature flags. Those latches are cleared by SPI command `HWCR.CL`.

Note: The over temperature and over current information is latched twice. When transmitting a clear latch command (`HWCR.CL`), the error flag is cleared during command transmission of the next SPI frame and ready for latching after the third raising edge of the SCLK signal. As a result, the first standard diagnosis information after a clear latch command will indicate a failure mode at the previously affected channels although the thermal latches have been cleared already. In case of continuous over load, the error flags are set again immediately because of the over load monitoring signal.

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8.2   Load Current Sense Diagnosis

There is a current sense signal available at pin IS which provides a current proportional to the load current of one selected channel. The selection is done by a multiplexer which is configured via SPI.

Current Sense Signal

The current sense signal (ratio $k_{ILIS} = I_L / I_S$) is provided during on-state as long as no failure mode occurs. The ratio k_{ILIS} can be adjusted to the load type (LED or bulb) via SPI register `HWCR` for channel 2 and 3. The accuracy of the ratio k_{ILIS} depends on the load current. Usually a resistor R_{IS} is connected to the current sense pin. It is recommended to use resistors 1.5 kΩ $< R_{IS} <$ 5 kΩ. A typical value is 2.7 kΩ.
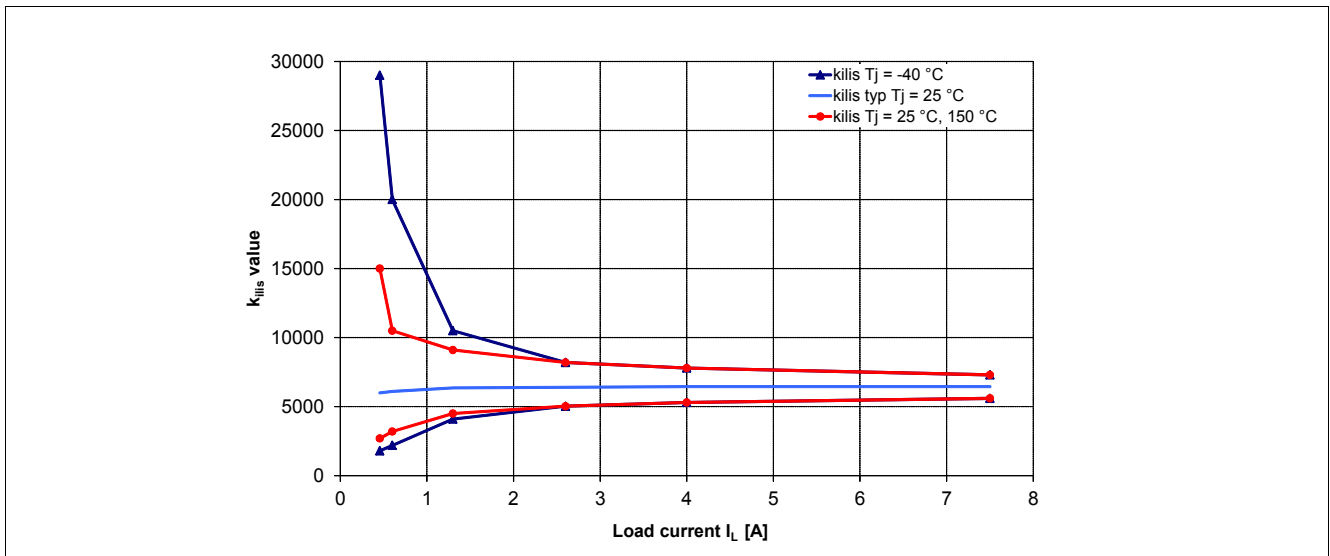

Figure 21   Current Sense Ratio k_{ILIS} Channel 0, 1 [1]
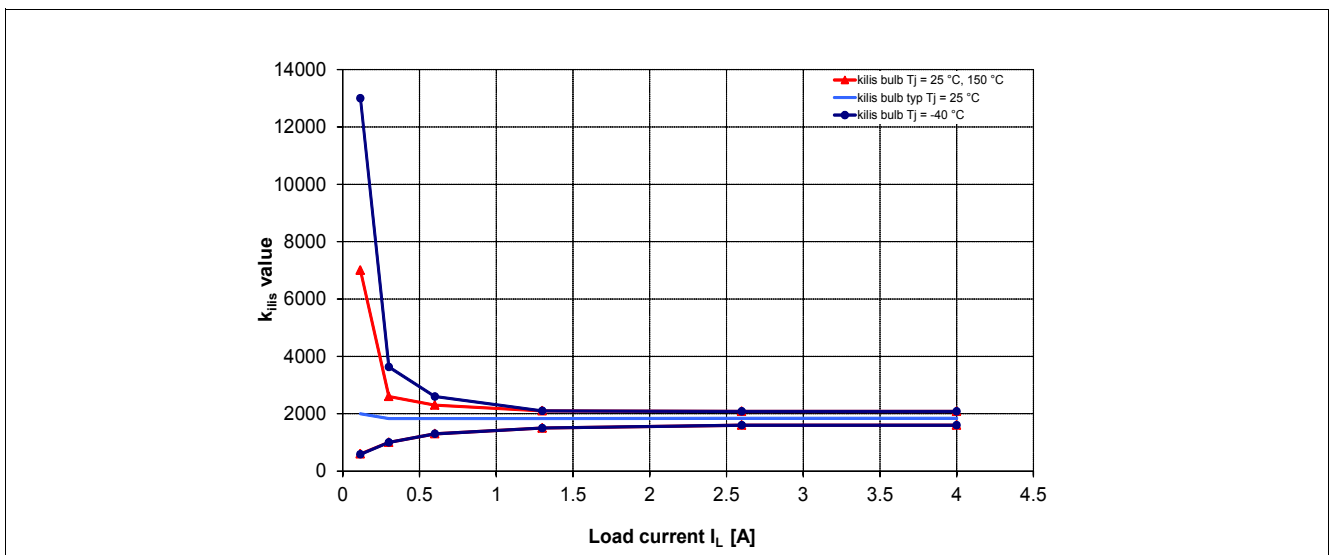

Figure 22   Current Sense Ratio k_{ILIS} Channel 2, 3 (bulb) [1]

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[1] The curves show the behavior based on characterization data. The marked points are guaranteed in this Data Sheet in **Section 8.5** (Position **8.5.1** and **8.5.2**).
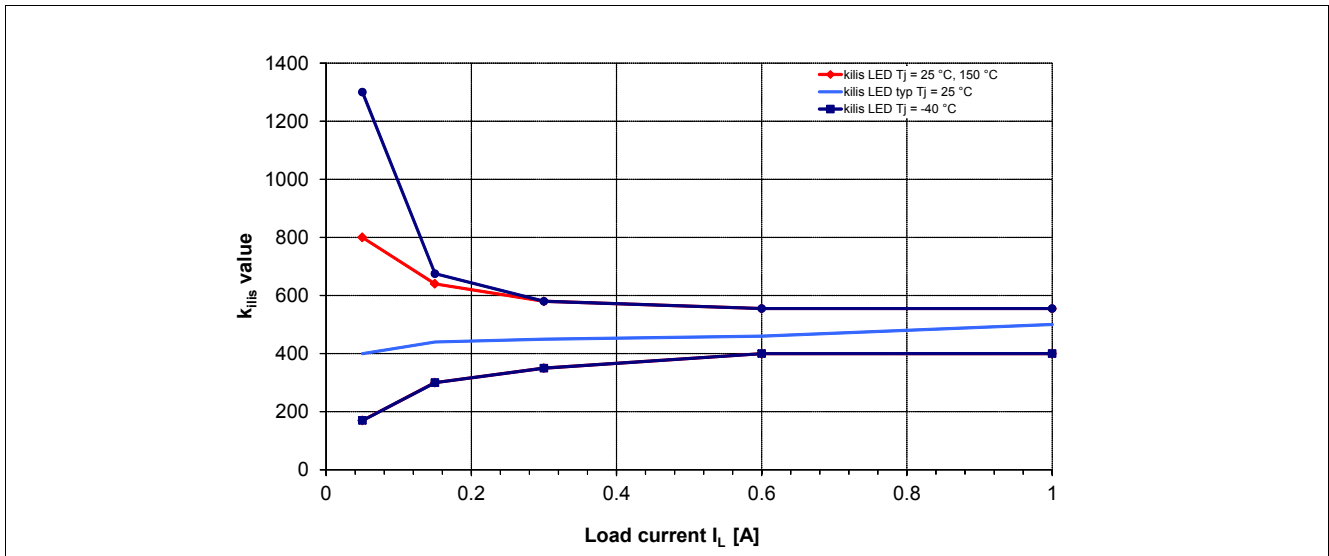
Figure 23   Current Sense Ratio k_{ILIS} Channel 2, 3 (LED) [1]

In case of OFF-state, over current, dynamic temperature sensor latch as well as over temperature, the current sense signal of the affected channel is switched off. To distinguish between a latched and non latched flag, the SPI diagnosis word can be used. The over current shut down flag ($n < n_{retry}$) is cleared every time the diagnosis is transmitted, whereas the over temperature latch, dynamic temperature protection latch and over current latch is cleared by a dedicated SPI command (`HWCR.CL`).

Details about timings between the current sense signal I_{IS} and the output voltage V_{OUT} and the load current I_L can be found in **Figure 24**.
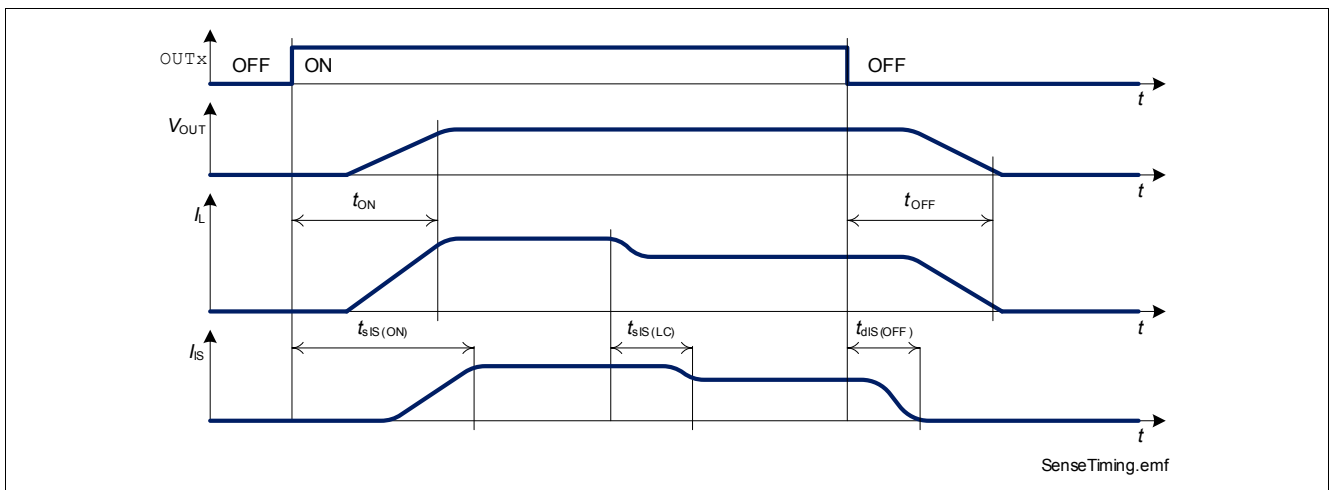

Figure 24   Timing of Current Sense Signal

Current Sense Multiplexer

There is a current sense multiplexer implemented in the SPOC - BTS5482SF that routes the sense current of the selected channel to the diagnosis pin IS. The channel is selected via SPI register `DCR.MUX`. The sense current also can be disabled by SPI register `DCR.MUX`. For details on timing of the current sense multiplexer, please refer to **Figure 25**.

The current sense diagnosis enable signal for the external smart power drivers also can be selected via the SPI register `DCR.MUX`. For being compliant to PROFET+ diagnostic functions, it is possible to configure pin EDD0 as DEN and EDD1 as DSEL. Therefore, the bit `OUTH.PRO+` needs to be set.
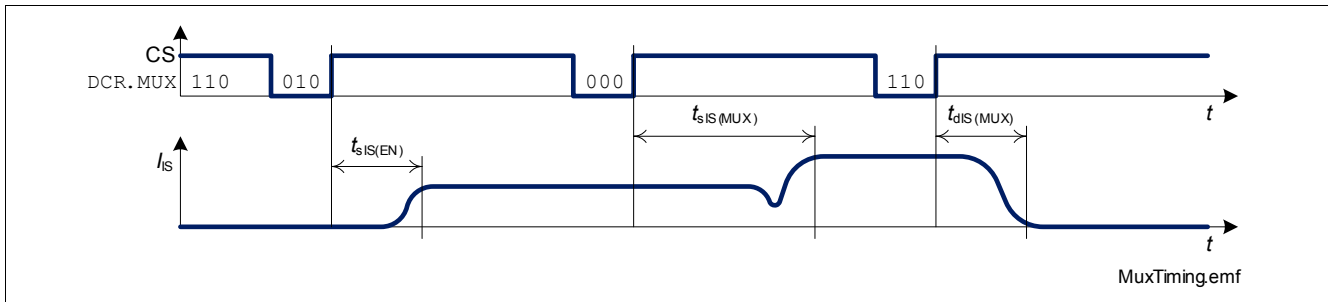
Figure 25   **Timing of Current Sense Multiplexer**

Current Sense Offset Trimming

To increase the current sense accuracy of SPOC - BTS5482SF, a circuitry to measure and trim the sense offset current is implemented. This so called calibration mode is activated by the SPI command `ICR.CAL = 1`$_b$. In calibration mode, a current proportional to the positive offset of the operational amplifier is provided on the IS pin. To increase the accuracy of the calibration this current is amplified when calibration mode is entered (see **8.5.4**). The offset of the operational amplifier can be trimmed by 15 steps which are selected by the bits `KILIS.OSTn`. (see. **Chapter 9.6** for detailed information). To exit the calibration mode `ICR.CAL` is set to `0`$_b$. During calibration the state of the current sense multiplexer should not be changed, otherwise the measured current could be affected. If `DCR.MUX = 111` the device exits calibration mode and stand-by mode is entered. In general the calibration mode does not have any effect on other SPI registers or functions of the device. In case of calibration during operation switching transients on the supply line must be considered.

8.3   Switch Bypass Diagnosis

To detect short circuit to V_S, there is a switch bypass monitor implemented for all internal channels. In case of short circuit between the output pin OUT and V_S in ON-state, the current will flow through the power transistor as well as through the short circuit (bypass) with undefined ratio. As a result, the current sense signal will show lower values than expected by the load current. In OFF-state, the output voltage will stay close to V_S potential which means a small V_{DS}. The time for the output voltage to reach a steady state condition depends on the time constant of the respective output pin which is affected by the resistance and capacitance introduced by external components and the board layout.

The switch bypass monitor compares the voltage V_{DS} across the power transistor of that channel, which is selected by the current sense multiplexer (`DCR.MUX`) with threshold $V_{DS(SB)}$. The result of the comparison can be read in SPI register `DCR.SBM` or in the standard diagnosis.

8.4   Open Load in OFF-State

For performing a dedicated open load in OFF-state detection a current source can be switched in parallel to the DMOS according to the **Figure 20**. The current source current can be programmed in two steps by the bit `ICR.CSL`.

The following procedure is recommended to use:

*   Select the dedicated channel with the multiplexer
*   Enable the open load current with the `DCR.CSOL` bit
*   Read the `DCR.SBM` or the standard diagnosis
*   Disable the open load current with the `DCR.CSOL` bit

Note: To distinguish between a short circuit to V_S and an open load in OFF-state, a pull-down resistor at the output would be needed to compensate the output leakage of the channel.

8.5 Electrical Characteristics

Electrical Characteristics Diagnosis

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Load Current Sense							
8.5.1	Current sense ratio	k_{ILIS}					T_j = -40 °C
	channel 0, 1:						
	0.456 A		1800	6900	29000		–
	0.600 A		2200	6700	20000		–
	1.3 A		4100	6400	10500		–
	2.6 A		5030	6400	8200		–
	4.0 A		5300	6450	7800		–
	7.5 A		5600	6450	7300		–
	channel 2, 3 (bulb):						HWCR.LEDn = 0
	0.115 A		585	2000	13000		–
	0.300 A		1000	1830	3630		–
	0.600 A		1300	1830	2600		–
	1.3 A		1500	1830	2100		–
	2.6 A		1600	1840	2080		–
	4.0 A		1600	1840	2080		–
	channel 2, 3 (LED):						HWCR.LEDn = 1
	0.050 A		170	400	1300		–
	0.150 A		300	440	675		–
	0.300 A		350	450	580		–
	0.600 A		400	460	555		–
	1.0 A		400	500	555		–
8.5.2	Current sense ratio	k_{ILIS}					T_j = 25 °C to 150 °C
	channel 0, 1:						
	0.456 A		2700	6000	15000		–
	0.600 A		3200	6100	10500		–
	1.3 A		4500	6350	9100		–
	2.6 A		5030	6400	8200		–
	4.0 A		5300	6450	7800		–
	7.5 A		5600	6450	7300		–
	channel 2, 3 (bulb):						HWCR.LEDn = 0
	0,115		600	1750	7000		–
	0.300 A		1000	1790	2600		–
	0.600 A		1300	1810	2300		–
	1.3 A		1500	1830	2100		–
	2.6 A		1600	1840	2080		–
	4.0 A		1600	1840	2080		–

Electrical Characteristics Diagnosis (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
	channel 2, 3 (LED):						HWCR.LEDn = 1
	0.050 A		170	400	800		–
	0.150 A		300	440	640		–
	0.300 A		350	450	580		–
	0.600 A		400	460	555		–
	1.0 A		400	500	555		–
8.5.3	Current sense drift of unaffected channel during inverse current of other channels	$\Delta k_{ILIS(IC)}$					[1] DCR.MUX ≠ 111 $I_{L0, 1}$ = 7.5 A $I_{L1, 0\,(IC)}$ = 7.5 A $I_{L2, 3\,(IC)}$ = 2.6 A
	channel 0, 1		-20 %	–	20 %		
			-20 %	–	20 %		
	channel 2, 3 (bulb)						HWCR.LEDn = 0 $I_{L2, 3}$ = 2.6 A $I_{L0, 1\,(IC)}$ = 7.5 A $I_{L3, 2\,(IC)}$ = 2.6 A
			-20 %	–	20 %		
			-20 %	–	20 %		
	channel 2, 3 (LED)						HWCR.LEDn = 1 $I_{L2, 3}$ = 0.6 A $I_{L0, 1\,(IC)}$ = 7.5 A $I_{L3, 2\,(IC)}$ = 2.6 A
			-20 %	–	20 %		
			-20 %	–	20 %		
8.5.4	Calibration step	$I_{IS(CAL)}$				µA	[1] T_j = 25 °C
			–	5	–		ICR.CAL = 0
			–	75	–		ICR.CAL = 1
8.5.5	Current sense voltage limitation	$V_{IS(LIM)}$	8	9.5	11	V	[1][2] I_{IS} = 3mA
8.5.6	Maximum steady state current sense output current	$I_{IS(MAX)}$	5.5	–	20	mA	[1] V_{IS} = 0 V
8.5.7	Current sense leakage / offset current	$I_{IS(en)}$				µA	I_L = 0 A DCR.MUX ≠ 111 ICR.CAL = 0 KILIS.OSTn = 1000
	channel 0, 1		–	–	70		
	channel 2, 3		–	–	70		
8.5.8	Current sense leakage, while diagnosis disabled	$I_{IS(dis)}$	–	–	1	µA	DCR.MUX = 110 ICR.CAL = 0

Electrical Characteristics Diagnosis (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		

8.5.9	Current sense settling time after channel activation
	
	channel 0, 1
	channel 2, 3
		$t_{sIS(ON)}$	
			
			–
			
			–
			
			–
				
				–
				
				–
				
				–
					
					150
					
					150
					
					100
						µs	V_S = 13.5 V
							R_{IS} = 2.7 kΩ
							R_L = 2.2 Ω
							`HWCR.LEDn = 0`
							R_L = 6.8 Ω
							`HWCR.LEDn = 1`
							R_L = 33 Ω

8.5.10	Current sense desettling time after channel deactivation	$t_{dIS(OFF)}$	
			
			–
			–
				
				–
				–
					
					25
					25
						µs	[1] V_S = 13.5 V
							R_{IS} = 2.7 kΩ
							`HWCR.LEDn = 0`
							`HWCR.LEDn = 1`

8.5.11	Current sense settling time after change of load current
	
	channel 0, 1
	channel 2, 3
		$t_{sIS(LC)}$	
			
			–
			
			–
			
			–
				
				–
				
				–
				
				–
					
					30
					
					30
					
					30
						µs	[1] V_S = 13.5 V
							R_{IS} = 2.7 kΩ
							I_L = 7.5 A to 4.0 A
							`HWCR.LEDn = 0`
							I_L = 2.6 A to 1.3 A
							`HWCR.LEDn = 1`
							I_L = 0.6 A to 0.3 A

8.5.12	Current sense settling time after current sense activation	$t_{sIS(EN)}$	–	–	25	µs	R_{IS} = 2.7 kΩ
							`DCR.MUX:`
							`110 -> 000`

8.5.13	Current sense settling time after multiplexer channel change	$t_{sIS(MUX)}$	–	–	30	µs	R_{IS} = 2.7 kΩ
							R_{L0} = 2.2 Ω
							R_{L2} = 33 Ω
							`DCR.MUX:`
							`010 -> 000`

8.5.14	Current sense deactivation time	$t_{dIS(MUX)}$	–	–	25	µs	[1] R_{IS} = 2.7 kΩ
							`DCR.MUX:`
							`000 -> 110`

Switch Bypass Monitor							
8.5.15	Switch bypass monitor threshold	$V_{DS(SB)}$	1.5	–	4	V	–
Open load in off current source							
8.5.16	Current source in OFF-state	$I_{L(OL)}$	100 3.0	– –	450 7.5	µA mA	`ICR.CSL = 0` `ICR.CSL = 1`

1) Not subject to production test, specified by design.

2) Voltage clamp at current sense pin has to be considered as a protection feature.

9 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) is a full duplex synchronous serial slave interface, which uses four lines: SO, SI, SCLK and $\overline{CS}$. Data is transferred by the lines SI and SO at the rate given by SCLK. The falling edge of $\overline{CS}$ indicates the beginning of an access. Data is sampled in on line SI at the falling edge of SCLK and shifted out on line SO at the rising edge of SCLK. Each access must be terminated by a rising edge of $\overline{CS}$. A modulo 8 counter ensures that data is taken only, when a multiple of 8 bit has been transferred. The interface provides daisy chain capability.
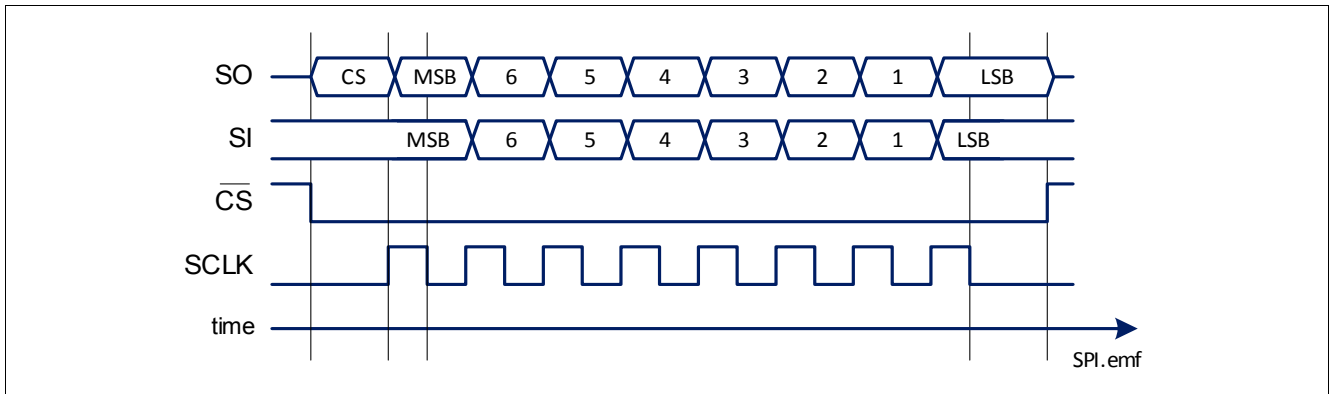

Figure 26   Serial Peripheral Interface

9.1 SPI Signal Description

$\overline{CS}$ **- Chip Select:**

The system micro controller selects the SPOC - BTS5482SF by means of the $\overline{CS}$ pin. Whenever the pin is in low state, data transfer can take place. When $\overline{CS}$ is in high state, any signals at the SCLK and SI pins are ignored and SO is forced into a high impedance state.

$\overline{CS}$ **High to Low transition:**

• The requested information is transferred into the shift register.
• SO changes from high impedance state to high or low state depending on the logic OR combination between the transmission error flag (TER) and the signal level at pin SI. As a result, even in daisy chain configuration, a high signal indicates a faulty transmission. This information stays available to the first rising edge of SCLK.
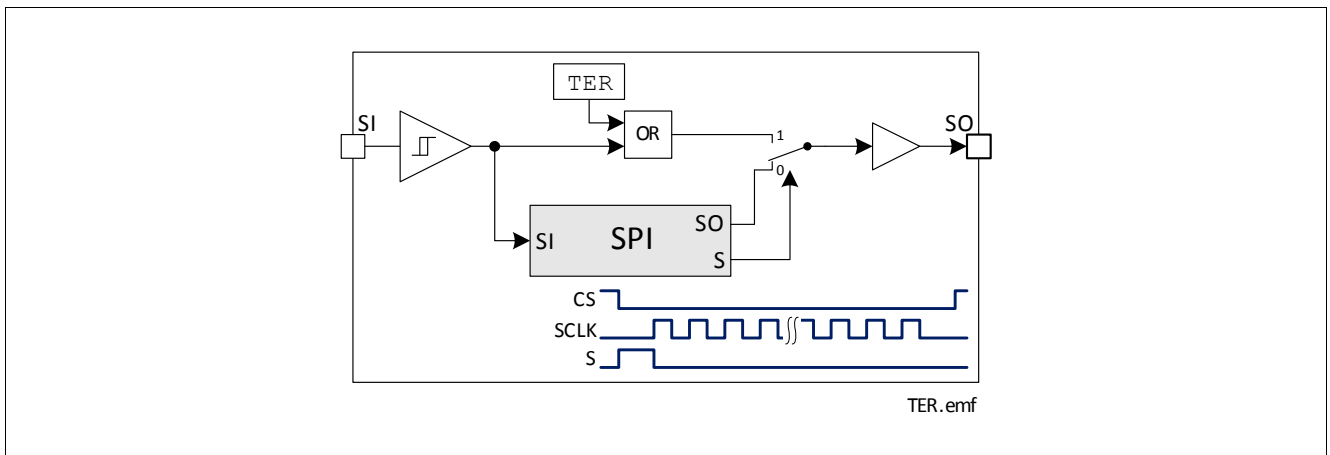

Figure 27   Combinatorial Logic for TER Flag

$\overline{\text{CS}}$ Low to High transition:

- Command decoding is only done, when after the falling edge of $\overline{\text{CS}}$ exactly a multiple (1, 2, 3, …) of eight SCLK signals have been detected. In case of faulty transmission, the transmission error flag (`TER`) is set and the command is ignored.
- Data from shift register is transferred into the addressed register.

SCLK - Serial Clock:

This input pin clocks the internal shift register. The serial input (SI) transfers data into the shift register on the falling edge of SCLK while the serial output (SO) shifts diagnostic information out on the rising edge of the serial clock. It is essential that the SCLK pin is in low state whenever chip select $\overline{\text{CS}}$ makes any transition.

SI - Serial Input:

Serial input data bits are shift-in at this pin, the most significant bit first. SI information is read on the falling edge of SCLK. The input data consists of two parts, control bits followed by data bits. Please refer to **Section 9.5** for further information.

SO Serial Output:

Data is shifted out serially at this pin, the most significant bit first. SO is in high impedance state until the $\overline{\text{CS}}$ pin goes to low state. New data will appear at the SO pin following the rising edge of SCLK. Please refer to **Section 9.5** for further information.

9.2 Daisy Chain Capability

The SPI of SPOC - BTS5482SF provides daisy chain capability. In this configuration several devices are activated by the same $\overline{\text{CS}}$ signal $\overline{\text{MCS}}$. The SI line of one device is connected with the SO line of another device (see **Figure 28**), in order to build a chain. The ends of the chain are connected with the output and input of the master device, MO and MI respectively. The master device provides the master clock MCLK which is connected to the SCLK line of each device in the chain.

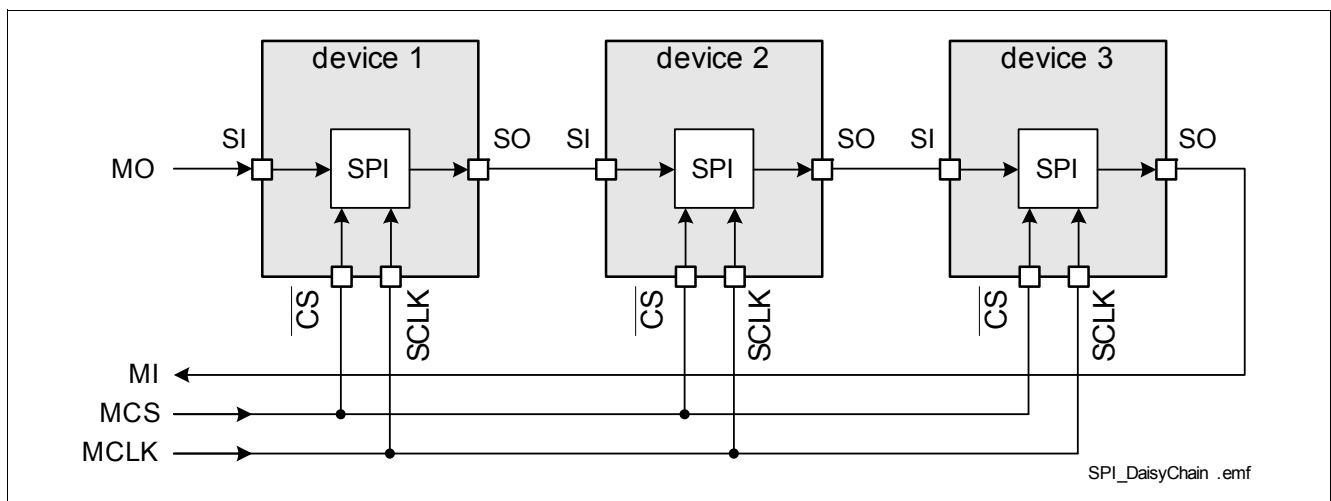**Figure 28   Daisy Chain Configuration**

In the SPI block of each device, there is one shift register where one bit from SI line is shifted in each SCLK. The bit shifted out occurs at the SO pin. After eight SCLK cycles, the data transfer for one device has been finished. In single chip configuration, the $\overline{CS}$ line must turn high to make the device accept the transferred data. In daisy chain configuration, the data shifted out at device 1 has been shifted in to device 2. When using three devices in daisy chain, three times eight bits have to be shifted through the devices. After that, the $\overline{MCS}$ line must turn high (see **Figure 29**).
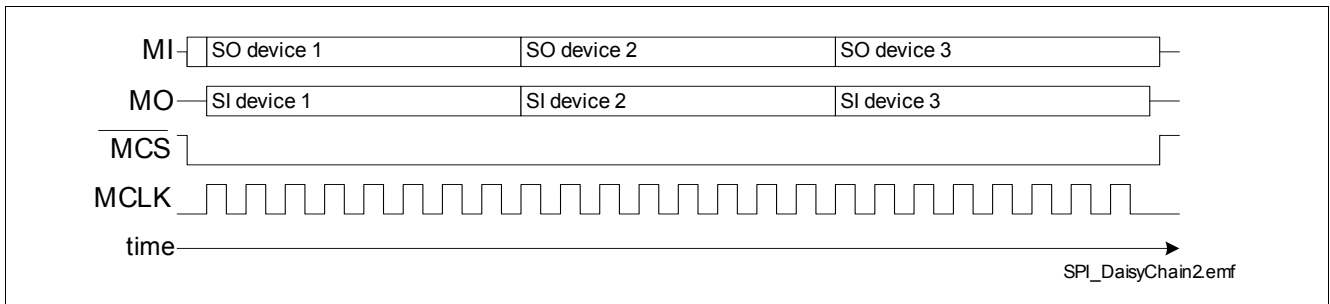

Figure 29   Data Transfer in Daisy Chain Configuration

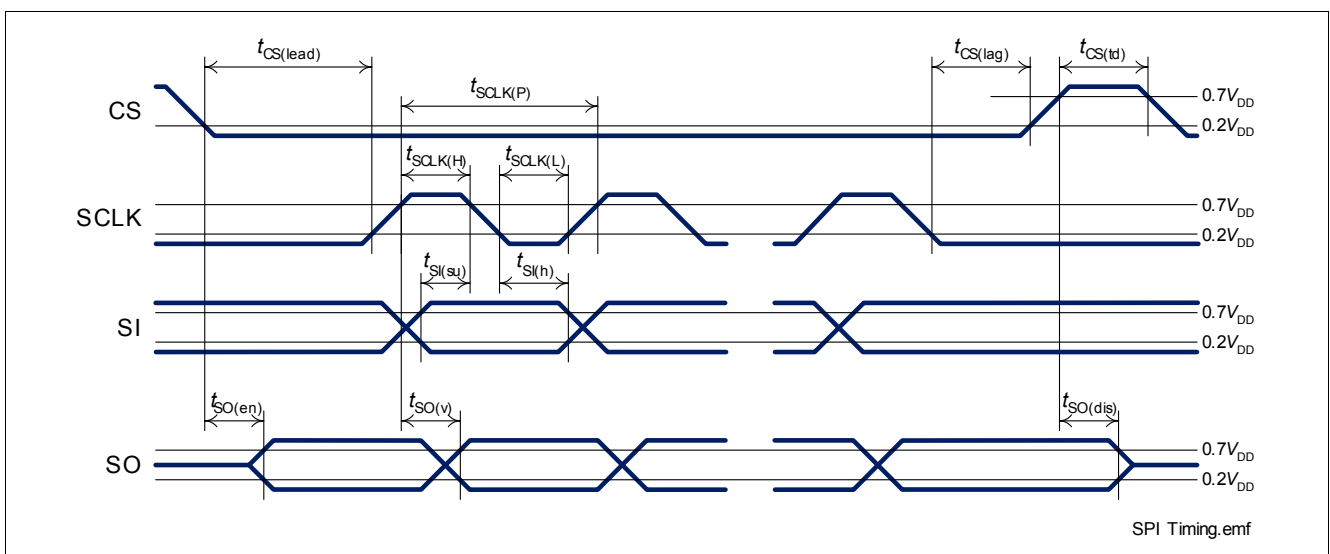## 9.3   Timing Diagrams

Figure 30   Timing Diagram SPI Access

9.4 Electrical Characteristics

Electrical Characteristics Serial Peripheral Interface (SPI)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
Input Characteristics ($\overline{CS}$, SCLK, SI)							
9.4.1	L level of pin $\quad$ $\overline{CS}$ $\quad$ $V_{CS(L)}$ $\quad$ SCLK $\quad$ $V_{SCLK(L)}$ $\quad$ SI $\quad$ $V_{SI(L)}$		0	–	$0.2*$ V_{DD}	V	V_{DD} = 4.3 V
9.4.2	H level of pin $\quad$ $\overline{CS}$ $\quad$ $V_{CS(H)}$ $\quad$ SCLK $\quad$ $V_{SCLK(H)}$ $\quad$ SI $\quad$ $V_{SI(H)}$		$0.4*$ V_{DD}	–	V_{DD}	V	V_{DD} = 4.3 V
9.4.3	Pull-up resistor at $\overline{CS}$ pin	R_{CS}	50	120	180	kΩ	[1]
9.4.4	Pull-down resistor at pin $\quad$ SCLK $\quad$ R_{SCLK} $\quad$ SI $\quad$ R_{SI}		50	120	180	kΩ	[1]
Output Characteristics (SO)							
9.4.5	L level output voltage	$V_{SO(L)}$	0	–	0.4	V	I_{SO} = -0.5 mA
9.4.6	H level output voltage	$V_{SO(H)}$	V_{DD} - 0.4 V	–	V_{DD}	V	I_{SO} = 0.5 mA V_{DD} = 4.3 V
9.4.7	Output tristate leakage current	$I_{SO(OFF)}$	-10	–	10	µA	$V_{CS} = V_{DD}$
Timings							
9.4.8	Serial clock frequency	f_{SCLK}	0 0	– –	5 3	MHz	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.9	Serial clock period	$t_{SCLK(P)}$	200 333	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.10	Serial clock high time	$t_{SCLK(H)}$	100 166	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.11	Serial clock low time	$t_{SCLK(L)}$	100 166	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.12	Enable lead time (falling $\overline{CS}$ to rising SCLK)	$t_{CS(lead)}$	200 333	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.13	Enable lag time (falling SCLK to rising $\overline{CS}$)	$t_{CS(lag)}$	200 333	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.14	Transfer delay time (rising $\overline{CS}$ to falling $\overline{CS}$)	$t_{CS(td)}$	200 333	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.15	Data setup time (required time SI to falling SCLK)	$t_{SI(su)}$	20 33	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V
9.4.16	Data hold time (falling SCLK to SI)	$t_{SI(h)}$	20 33	– –	– –	ns	[1] V_{DD} = 4.3 V [2] V_{DD} = 3.0 V

Electrical Characteristics Serial Peripheral Interface (SPI) (cont'd)

Unless otherwise specified: V_S = 8 V to 17 V, V_{DD} = 3.0 V to 5.5 V, T_j = -40 °C to +150 °C
typical values: V_S = 13.5 V, V_{DD} = 4.3 V, T_j = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
9.4.17	Output enable time (falling $\overline{CS}$ to SO valid)	$t_{SO(en)}$				ns	[2] C_L = 20 pF
			–	–	200		V_{DD} = 4.3 V
			–	–	333		V_{DD} = 3.0 V
9.4.18	Output disable time (rising $\overline{CS}$ to SO tri-state)	$t_{SO(dis)}$				ns	[2] C_L = 20 pF
			–	–	200		V_{DD} = 4.3 V
			–	–	333		V_{DD} = 3.0 V
9.4.19	Output data valid time with capacitive load	$t_{SO(v)}$				ns	[2] C_L = 20 pF
			–	–	100		V_{DD} = 4.3 V
			–	–	166		V_{DD} = 3.0 V

1) Not subject to production test, specified by design. SPI functional test is performed at f_{SCLK} = 5 MHz.
2) Not subject to production test, specified by design.

9.5 SPI Protocol 8 Bit

CS[1]	7	6	5	4	3	2	1	0
	Write OUTL, OUTH and KILIS Register							
SI	1	0	ADDR		DATA			
	Read OUTL, OUTH and KILIS Register							
SI	0	0	ADDR		x	x	x	0
	Write Configuration and Control Registers							
SI	1	1	ADDR		DATA			
	Read Configuration and Control Registers							
SI	0	1	ADDR		x	x	x	0
	Read Standard Diagnosis							
SI	0	x	x	x	x	x	x	1
	Standard Diagnosis							
SO	TER	0	LHI	SBM	x	ERR3	ERR2	ERR1	ERR0
	Second Frame of Read Command							
SO	TER	1	0	OUT5	OUT4	OUT3	OUT2	OUT1	OUT0
SO	TER	1	1	ADDR		DATA			

1) The SO pin shows this information between $\overline{CS}$ hi -> lo and first SCLK lo -> hi transition.

Note: Reading a register needs two SPI frames. In the first frame the RD command is sent. In the second frame the output at SPI signal SO will contain the requested information. A new command can be executed in the second frame. The standard diagnosis can be accessed either by sending the standard diagnosis read command or it is transmitted after each write command.

Field	Bits	Type	Description
W/$\overline{R}$	7	w	0 Read 1 Write
RB	6	r	**Register Bank** **0** Read / write to OUTL, OUTH and KILIS register 1 Read / write to the other register
TER	CS	r	**Transmission Error** **0** Previous transmission was successful (modulo 8 clocks received) 1 Previous transmission failed or first transmission after reset
ADDR	6:5	rw	**Address** Pointer to register for read and write command
DATA	4:0	rw	**Data** Data written to or read from register selected by address ADDR
ERRn n = 3 to 0	n	r	**Diagnosis of Channel n** [1] **0** No failure 1 Over temperature, over current, over load or short circuit for channel 0 to 3
SBM	5	r	**Switch Bypass Monitor** [2] 0 $V_{DS} < V_{DS(SB)}$ 1 $V_{DS} > V_{DS(SB)}$

Field	Bits	Type	Description
OUTn n = 5 to 0	n	r	**Output Status for Channel n** **0** Channel is switched off 1 Channel is switched on
LHI	6	r	**Limp Home Enable** [3)] 0 H-input signal at LHI pin 1 L-input signal at LHI pin

1) No ERR-flags available for external drivers

2) Invalid in stand-by mode

3) Not latching information, read of LHI-status during falling CS

9.6 Register Overview

RB	Address		Name	Description
0	0	0	OUTL	Output Configuration Register Low
0	0	1	OUTH	Output Configuration Register High
0	1	0	KILIS	Current Sense Offset Calibration Register
0	1	1	SCCR	Short Circuit Configuration Register
1	0	1	ICR	Input and Current Source Configuration Register
1	1	0	HWCR	Hardware Configuration Register
1	1	1	DCR	Diagnosis Control Register

Bit	7	6	5	4	3	2	1	0	
Name	W/$\overline{R}$	RB	ADDR		DATA				default [1)]
OUTL	W/R	0	0	0	OUT3	OUT2	OUT1	OUT0	80$_H$
OUTH	W/R	0	0	1	PRO+	res.	OUT5	OUT4	90$_H$
KILIS	W/R	0	1	0	OST3	OST2	OST1	OST0	A8$_H$
SCCR	W/R	0	1	1	ITC3	ITC2	ITC1	ITC0	B0$_H$
ICR	W/R	1	0	1	COL	INCG	CSL	CAL	D0$_H$
HWCR	R	1	1	0	LED3	LED2	STB	CL	E2$_H$
	W	1	1	0	LED3	LED2	RST	CL	-
DCR	R	1	1	1	SBM	MUX			F7$_H$
	W	1	1	1	CSOL	MUX			-

1) The default values are set after reset.

Note: A readout of an unused register will return the standard diagnosis.

Field	Bits	Type	Description
OUTL n = 3 to 0	n	rw	**Output Control Register for Channel 0 to 3** **0** OFF 1 ON
OUTH n = 3 to 0	n	rw	**Output Control Register for Channel 4, 5 and PRO+ bit** **0** OFF 1 ON
PRO+	0	rw	**Configuration of EDD0 and EDD1 to be Compliant to PROFET+ Concept** **0** Normal mode 1 EDD0=DEN, EDD1=DSEL
OSTn n = 3 to 0	n	rw	**IS Offset Trimming** 0000 $I_{IS(EN)}$ - 8 x $I_{IS(CAL)}$ 0001 $I_{IS(EN)}$ - 7 x $I_{IS(CAL)}$ 0010 $I_{IS(EN)}$ - 6 x $I_{IS(CAL)}$ 0011 $I_{IS(EN)}$ - 5 x $I_{IS(CAL)}$ 0100 $I_{IS(EN)}$ - 4 x $I_{IS(CAL)}$ 0101 $I_{IS(EN)}$ - 3 x $I_{IS(CAL)}$ 0110 $I_{IS(EN)}$ - 2 x $I_{IS(CAL)}$ 0111 $I_{IS(EN)}$ - 1 x $I_{IS(CAL)}$ **1000** $I_{IS(EN)}$ without Offset calibration 1001 $I_{IS(EN)}$ + 1 x $I_{IS(CAL)}$ 1010 $I_{IS(EN)}$ + 2 x $I_{IS(CAL)}$ 1011 $I_{IS(EN)}$ + 3 x $I_{IS(CAL)}$ 1100 $I_{IS(EN)}$ + 4x $I_{IS(CAL)}$ 1101 $I_{IS(EN)}$ + 5 x $I_{IS(CAL)}$ 1110 $I_{IS(EN)}$ + 6 x $I_{IS(CAL)}$ 1111 $I_{IS(EN)}$ + 7 x $I_{IS(CAL))}$
ITCn n = 3 to 0	n	rw	**Inrush Timer Control** **0** Timer $t_{delay(Htrip)}$ will run only in OFF state of respective channel 1 Timer $t_{delay(Htrip)}$ will run in ON and OFF state of respective channel
CAL	0	rw	**IS Offset Calibration** **0** Calibration mode is deactivated 1 Calibration mode is activated
CSL	1	rw	**Level for Current Source for Open Load Detection** **0** Low level 1 High level
INCG	2	rw	**Input Drive Configuration** **0** Direct drive mode 1 Assigned drive mode
COL	3	rw	**Input Combinatorial Logic Configuration** **0** Input signal OR-combined with according `OUTL` register bit 1 Input signal AND-combined with according `OUTL` register bit
STB	1	r	**Standby Mode** 0 Device is awake **1** Device is in Standby mode

Field	Bits	Type	Description
LEDn n = 3 to 2	n	rw	**Set LED Mode for Channel n** **0** Channel n is in bulb mode **1** Channel n is in LED mode
CL	0	rw	**Clear Latch** **0** Thermal and over current latches are untouched **1** Command: Clear all thermal and over current latches
RST	1	w	**Reset Command** **0** Normal operation **1** Execute reset command
MUX	2:0	rw	**Set Current Sense Multiplexer Configuration in OFF-state** 000 IS pin is high impedance 001 IS pin is high impedance 010 IS pin is high impedance 011 IS pin is high impedance 100 `OUTH.PRO+ = 0`: Diagnosis enable of external driver 0 activated (EDD0 = 1) 101 `OUTH.PRO+ = 0`: Diagnosis enable of external driver 1 activated (EDD1 = 1) 100 `OUTH.PRO+ = 1`: EDD0 = 1, EDD1 = 0 101 `OUTH.PRO+ = 1`: EDD0 = 1, EDD1 = 1 110 IS pin is high impedance **111** Stand-by mode (IS pin is high impedance) **Set Multiplexer Configuration in ON-state** 000 Current sense of channel 0 is routed to IS pin 001 Current sense of channel 1 is routed to IS pin 010 Current sense of channel 2 is routed to IS pin 011 Current sense of channel 3 is routed to IS pin 100 `OUTH.PRO+ = 0`: Diagnosis enable of external driver 0 activated (EDD0 = 1) 101 `OUTH.PRO+ = 0`: Diagnosis enable of external driver 1 activated (EDD1 = 1) 100 `OUTH.PRO+ = 1`: EDD0 = 1, EDD1 = 0 101 `OUTH.PRO+ = 1`: EDD0 = 1, EDD1 = 1 110 IS pin is high impedance **111** Stand-by mode (IS pin is high impedance))
SBM	3	r	**Switch Bypass Monitor [1]** 0 $V_{DS} < V_{DS(SB)}$ 1 $V_{DS} > V_{DS(SB)}$
CSOL	3	w	**Current Source Switch for Open Load Detection** **0** OFF **1** ON

1) Invalid in stand-by mode

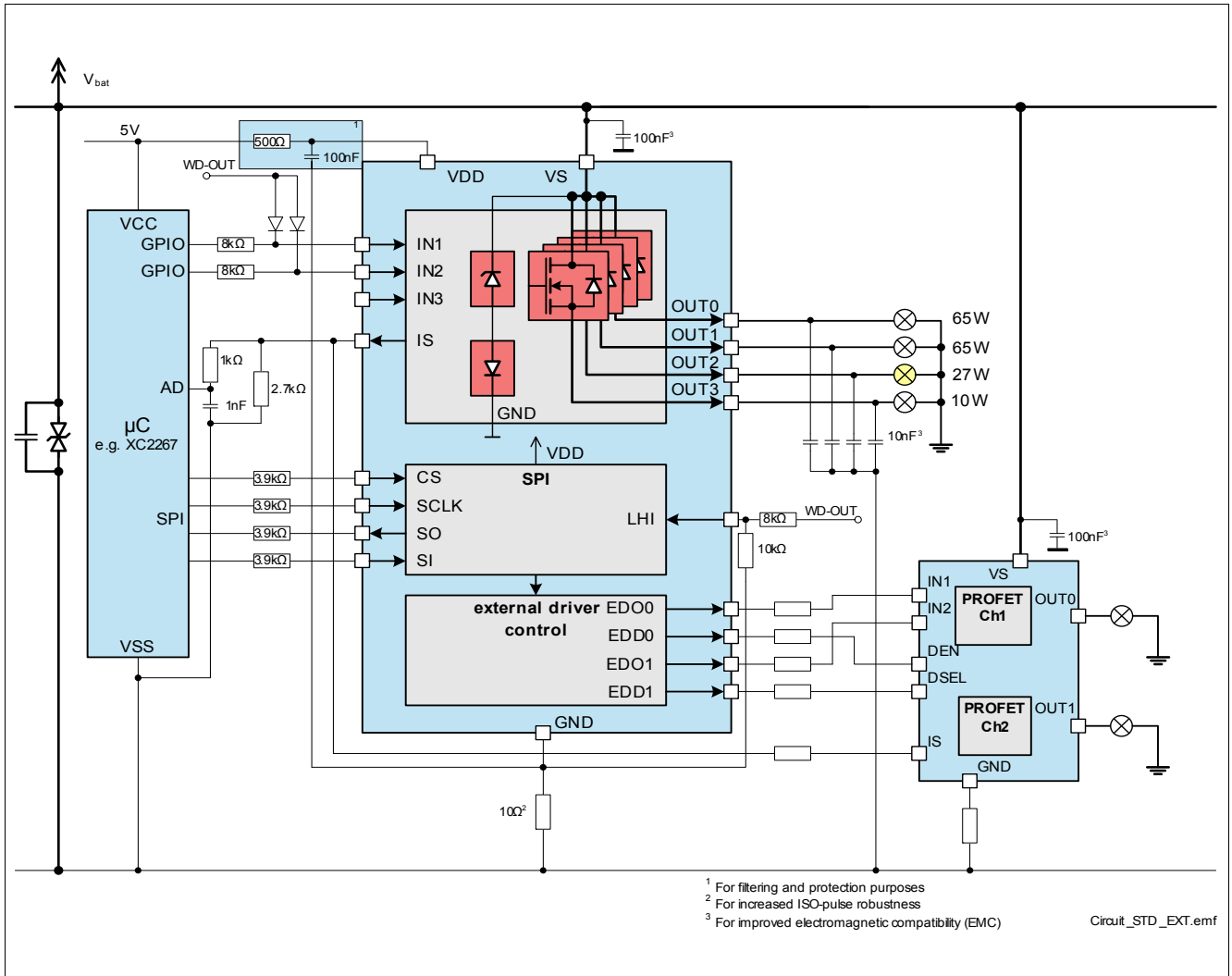# 10 Application Description

Figure 31 Application Circuit Example
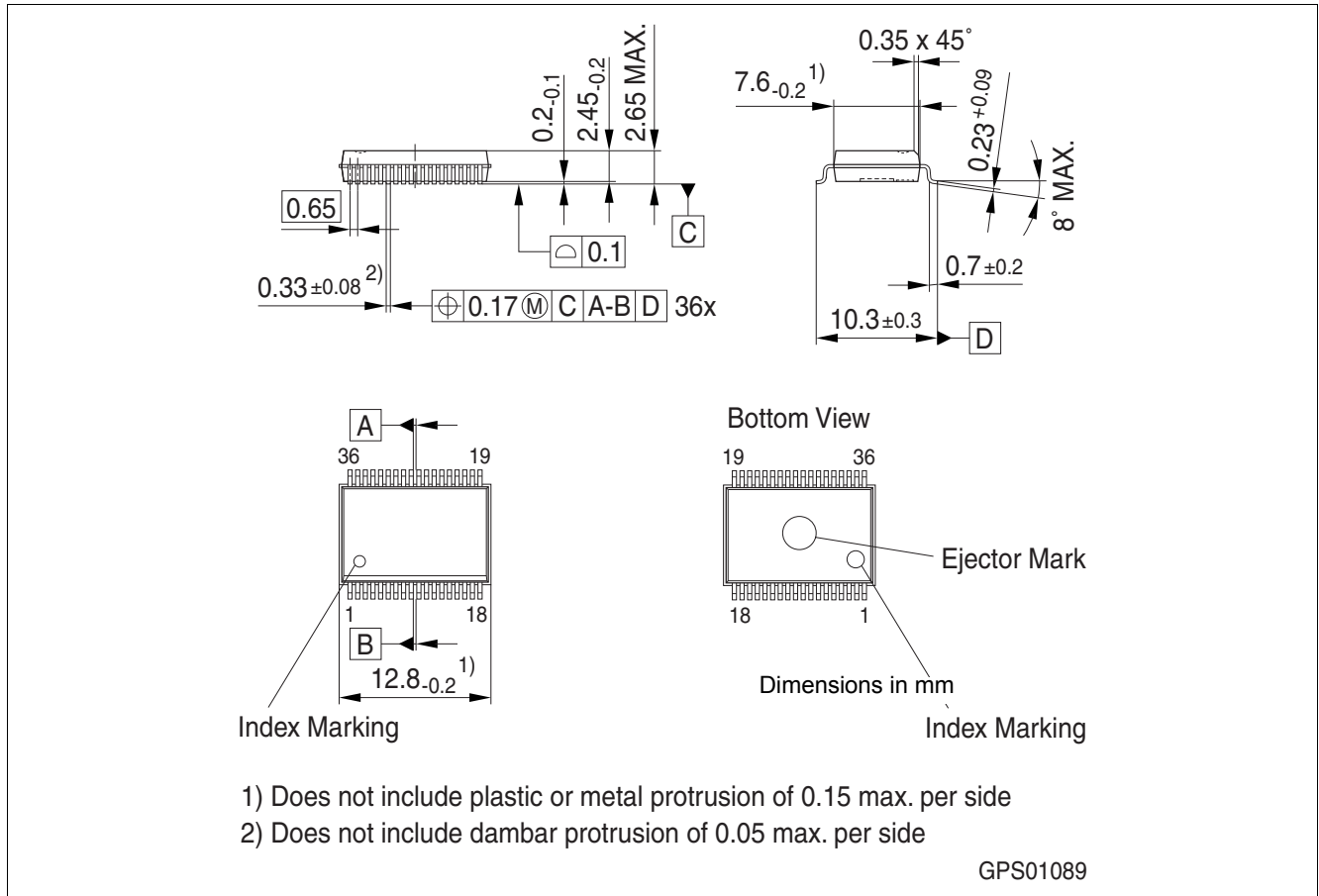
11   Package Outlines SPOC - BTS5482SF

Figure 32   PG-DSO-36-43 (Plastic Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

You can find all of our packages, sorts of packing and others in our Infineon Internet Page
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12   Revision History

Revision	Date	Changes
1.0	2013-06-05	Data Sheet

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